
Hardware Development Guide for i.MX 6SoloX Application Processors

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Chapter 1

About this Book

1.1 Overview

This document's purpose is to help hardware engineers design and test their i.MX 6 series processor based designs. It provides information on board layout recommendations, design checklists to ensure first-pass success and ways to avoid board bring-up problems. It also provides information on board-level testing and simulation such as using BSDL for board-level testing, using the IBIS model for electrical integrity simulation and more.

Engineers are expected to have a working understanding of board layouts and terminology, IBIS modeling, BSDL testing and common board hardware terminology.

This guide is released along with relevant device-specific hardware documentation such as datasheets, reference manuals and application notes available on www.nxp.com.

1.1.1 Devices supported

This Hardware Developer's Guide currently supports the i.MX 6SoloX.

1.2 Essential reference

This guide is intended as a companion to the i.MX 6 series chip reference manuals and data sheets. For reflow profile and thermal limits during soldering, see *General Soldering Temperature Process Guidelines* (document [AN3300](#)). These documents are available on www.nxp.com.

1.3 Suggested reading

This section lists additional reading that provides background for the information in this manual as well as general information about the architecture.

1.3.1 General Information

The following documentation provides useful information about the ARM processor architecture and computer architecture in general:

For information about the ARM Cortex-A9 processor see: <http://www.arm.com/products/processors/cortex-a/cortex-a9.php>

- **Computer Architecture: A Quantitative Approach** (Fourth Edition) - by John L. Hennessy and David A. Patterson
- **Computer Organization and Design: The Hardware/Software Interface** (Second Edition), by David A. Patterson and John L. Hennessy

The following documentation provides useful information about high-speed board design:

- **Right the First Time- A Practical Handbook on High Speed PCB and System Design - Volumes I & II** - Lee W. Ritchey (Speeding Edge) - ISBN 0-9741936-0-72
- **Signal and Power Integrity Simplified** (2nd Edition) - Eric Bogatin (Prentice Hall)- ISBN 0-13-703502-0
- **High Speed Digital Design- A Handbook of Black Magic** - Howard W. Johnson & Martin Graham (Prentice Hall) - ISBN 0-13-395724-1
- **High Speed Signal Propagation- Advanced Black Magic** - Howard W. Johnson & Martin Graham - (Prentice Hall) - ISBN 0-13-084408-X
- **High Speed Digital System Design- A handbook of Interconnect Theory and Practice** - Hall, Hall and McCall (Wiley Interscience 2000) - ISBN 0-36090-2
- **Signal Integrity Issues and Printed Circuit Design** - Doug Brooks (Prentice Hall) ISBN 0-13-141884-X
- **PCB Design for Real-World EMI Control** - Bruce R. Archambeault (Kluwer Academic Publishers Group) - ISBN 1-4020-7130-2
- **Digital Design for Interference Specifications** - A Practical Handbook for EMI Suppression - David L. Terrell & R. Kenneth Keenan (Newnes Publishing) - ISBN 0-7506-7282-X
- **Electromagnetic Compatibility Engineering** - Henry Ott (1st Edition - John Wiley and Sons) - ISBN 0-471-85068-3

- **Introduction to Electromagnetic Compatibility** - Clayton R. Paul (John Wiley and Sons) - ISBN 978-0-470-18930-6
- **Grounding & Shielding Techniques** - Ralph Morrison (5th Edition - John Wiley & Sons) - ISBN 0-471-24518-6
- **EMC for Product Engineers** - Tim Williams (Newnes Publishing) - ISBN 0-7506-2466-3

1.4 Related documentation

NXP documentation is available from the sources listed on the back page of this guide.

Additional literature is published as new NXP products become available. For a current list of documentation, see www.nxp.com.

1.5 Conventions

This document uses the following notational conventions:

| | |
|------------------|---|
| <i>Courier</i> | Used to indicate commands, command parameters, code examples, and file and directory names. |
| <i>Italics</i> | Italics indicates command or function parameters. |
| Bold | Function names are written in bold. |
| cleared/set | When a bit takes the value zero, it is said to be cleared; when it takes a value of one, it is said to be set. |
| mnemonics | Instruction mnemonics are shown in lowercase bold. |
| sig_name | Internal signals are written in all lowercase. |
| <i>nnnn nnnh</i> | Denotes hexadecimal number. |
| 0b | Denotes binary number. |
| rA, rB | Instruction syntax used to identify a source GPR. |
| rD | Instruction syntax used to identify a destination GPR. |
| REG[FIELD] | Abbreviations for registers are shown in uppercase text. Specific bits, fields, or ranges appear in brackets. For example, MSR[LE] refers to the little-endian mode enable bit in the machine state register. |
| x | In some contexts, such as signal encodings, an unitalicized x indicates a don't care. |
| <i>x</i> | An italicized x indicates an alphanumeric variable. |
| <i>n, m</i> | An italicized <i>n</i> or <i>m</i> indicates a numeric variable. |

NOTE

In this guide, notation for all logical, bit-wise, arithmetic, comparison, and assignment operations follow C Language conventions.

1.6 Signal conventions

_b, _B

Notation indicates that a signal is active when low.

signal_name

Lowercase italics is used to indicate internal signals.

1.7 Acronyms and abbreviations

The following table defines the acronyms and abbreviations used in this document.

Table 1-1. Definitions and acronyms

| Term | Definition |
|-------|---|
| ARM® | Advanced RISC machines processor architecture |
| BGA | Ball grid array package |
| BOM | Bill of materials |
| BSDL | Boundary scan description language |
| CAN | Flexible Controller Area Network peripheral |
| CCM | Clock Controller Module |
| CSI | MIPI camera serial interface |
| DDR | Dual data rate DRAM |
| DDR3 | DDR3 DRAM |
| DDR3L | Low voltage DDR3 DRAM |
| DDR3U | Ultra low voltage DDR3 DRAM |
| DRAM | Dynamic random access memory |
| ECSPI | Enhanced Configurable SPI peripheral |
| EIM | External Interface Module |
| ENET | 10/100/1000-Mbps Ethernet MAC peripheral |
| EPIT | Enhanced Periodic Interrupt Timer peripheral |
| ESR | Equivalent series resistance (of a crystal) |
| FSL | Freescale Semiconductor |
| GND | Ground |
| GPC | General Power Controller |
| GPIO | General-purpose input/output |
| HDCP | High-bandwidth Digital Content Protection |
| I2C | Inter-integrated circuit interface |
| IBIS | Input output buffer information specification |
| IOMUX | i.MX6 chip-level I/O multiplexing |
| JTAG | Joint Test Action Group |

Table continues on the next page...

Table 1-1. Definitions and acronyms (continued)

| | |
|---------|--|
| KPP | Keypad Port peripheral |
| LDB | LVDS Display bridge |
| LDO | Low drop-out regulator |
| LPCG | Low power clock gating |
| LPDDR2 | Low-power DDR2 DRAM |
| LVDS | Low-voltage differential signaling |
| MLB | MediaLB 150 peripheral |
| MMDC | Multi Mode DDR Controller |
| ODT | On-die termination |
| OTP | One-time programmable |
| PCB | Printed circuit board |
| PCIe | PCI Express |
| PCISig | Peripheral Component Interconnect Special Interest Group |
| PMIC | Power management integrated circuit |
| POR | Power-on reset |
| RAM | Random access memory |
| RGMII | Reduced Gigabit Media Independent Interface (Ethernet) |
| RMII | Reduced Media Independent Interface (Ethernet) |
| ROM | Read-only memory |
| SDMA | Smart Direct Memory Access Controller |
| UART | Universal asynchronous receiver/transmitter |
| USB | Universal Serial Bus |
| USB OTG | USB On-the-go |
| USB2.0 | USB version 2.0 peripheral |

Chapter 2

i.MX 6SoloX Design Checklist

2.1 Overview

This document provides a design checklist for the i.MX 6SoloX processor.

The design checklist tables contain recommendations for optimal design. Where appropriate, the checklist tables also provide an explanation of the recommendation so that users have a greater understanding of why certain techniques are recommended. All supplemental tables referenced by the checklist appear in sections following the design checklist tables.

2.2 Design Checklist Tables

Table 2-1. DDR recommendations

| Checkbox | Recommendation | Explanation/supplemental recommendation |
|----------|---|--|
| | 1. Connect ZQPAD to an external 240 Ω 1% resistor to GND. | This is a reference used during DRAM output buffer driver calibration. |
| | 2. Connect DRAM_VREF to a source that is 50% of the voltage value of NVCC_DRAM. | <ul style="list-style-type: none">The user may tie DDR_VREF to a precision external resistor divider. Shunt DDR_VREF to GND with a closely-mounted 0.1 μF capacitor. See Table 2-14 for resistor values. Using resistors with recommended tolerances ensures the $\pm 2\%$ DDR_VREF tolerance per the DDR3 specification.The user can use a PMIC's tracking regulator as used on NXP reference designs. |
| | 3. Connect DRAM_RESET to a 10 k Ω 5% pulldown resistor to GND. | <ul style="list-style-type: none">DDR3: DRAM_RESET should be pulled down to meet the JEDEC sequence until the controller is configured and starts driving. DRAM_RESET should be kept high when DDR3 enters self-refresh mode.LPDDR2: DRAM_RESET should be left unconnected. <p>Some NXP reference designs use a 1% resistor simply to consolidate the BOM.</p> |

Table continues on the next page...

Table 2-1. DDR recommendations (continued)

| | | |
|--|--|--|
| | | DRAM_RESET is an active-low signal. |
| | 4 . DRAM_SDCKE0 and DRAM_SDCKE1 require external pull-down resistors to GND for JEDEC compliance when using LPDDR2. | <ul style="list-style-type: none"> For LPDDR2: SDCKE[1:0] must be pulled down to meet the JEDEC sequence until the controller is configured and starts driving. NXP designs use 10 kΩ. For DDR3: SDCKE[1:0] pull-down is not required to meet JEDEC. |
| | 5 . DRAM_SDCKE0 and DRAM_SDCKE1 require external resistors (such as 10 kΩ) to GND to minimize current drain during deep sleep mode (DSM). | <p>The BSP (Board Support Package) uses a common DDR routine for both fly-by and T-topology designs. Fly-by designs have parallel resistor termination on address lines, while T-topology does not.</p> <p>During low-power self-refresh, the BSP programs pad control register GRP_CTLDS to 0x00000000.</p> <p>Therefore, DRAM_SDCKE0, DRAM_SDCKE1, and other associated GRP_CTLDS I/O are forced to the high-impedance state.</p> <p>Because DRAM_SDCKE0 and DRAM_SDCKE1 are forced to high-Z, external pull-down resistors are required to avoid floating outputs during standby. In NXP designs, 10 kohm resistors are utilized for this purpose. Any other termination on the DRAM_SDCKE0 and DRAM_SDCKE1 lines (such as 50 ohms) should not be present; simulation should be performed to ensure CKE signal integrity.</p> |
| | 6. Make sure that the correct LPDDR2 function is connected to the correct I/O. Note that this does not necessarily correspond to the I/O name. | MMDC IO names are for the DDR3 default. When LPDDR2 is selected, the I/O name (DDR3 MMDC PAD) does not match with the LPDDR2 functionality. See the “LPDDR2 and DDR3 pin mux mapping” table in the “Multi Mode DDR Controller (MMDC)” chapter in your chip reference manual. |

Table 2-2. LCD1 recommendations for developer’s boot modes

| Checkbox | Recommendation | Explanation/supplemental recommendation |
|----------|---|--|
| | 1. When LCD1 boot signals are used as the system’s LCD1 signals, other functions, or GPIO outputs after boot, use a passive resistor network to select the desired boot mode for development boards. | <p>Because only resistors are used, LCD1 bus loads can cause current drain, leading to higher (false) supply current measurements. Each LCD1 boot signal should connect to a series resistor to isolate the bus from the resistors and/or switchers; see Figure 2-1. Each configured LCD1 boot signal sees either a 14.7 kΩ pulldown or a 4.7 kΩ pullup. For each switch-enabled pulled-up signal, the supply is presented with a 10 kΩ current load.</p> <p>An alternate approach using buffers is implemented in the SABRE-SD development board design. Either of these implementations is acceptable.</p> |
| | <p>2. To reduce incorrect boot-up mode selections, do one of the following:</p> <ul style="list-style-type: none"> Use LCD1 boot interface lines only as processor outputs. Ensure LCD1 boot interface lines are not loaded down such that the level is interpreted as | Using LCD1 boot interface lines as inputs may result in a wrong boot up due to the source overcoming the pull resistor value. A peripheral device may require the LCD1 signal to have an external or on-chip resistor to minimize signal floating. |

Table continues on the next page...

Table 2-2. LCD1 recommendations for developer's boot modes (continued)

| | | |
|--|--|--|
| | <p>low during power-up, when the intent is to be a high level, or vice versa.</p> <ul style="list-style-type: none"> If an LCD1 boot signal must be configured as an input, isolate the LCD1 signal from the target driving source with one analog switch and apply the logic value with a second analog switch. Alternately, peripheral devices with three-state outputs may be used; ensure the output is high-impedance during the boot up interval. | <p>If the usage of the LCD1 boot signal affects the peripheral device, then an analog switch, open collector buffer, or equivalent should isolate the path. A pullup or pulldown resistor at the peripheral device may be required to maintain the desired logic level. Review the switch or device data sheet for operating specifications.</p> |
| | <p>3. The BOOT_CFG signals are required for proper functionality and operation and should not be left floating</p> | <p>See the "System Boot" chapter in your chip reference manual for the correct boot configuration. Note that an incorrect setting may result from an improper booting sequence.</p> |

Table 2-3. Boot mode input recommendations

| Checkbox | Recommendation | Explanation/supplemental recommendation |
|----------|---|--|
| | <p>1. For BOOT_MODE1 and BOOT_MODE0, use one of the following options to achieve logic 0:</p> <ul style="list-style-type: none"> Tie to GND through any size external resistor Tie directly to GND Float <p>For logic 1, use one of the following:</p> <ul style="list-style-type: none"> Tie directly to the VDD_SNVS_IN rail Tie to the VDD_SNVS_IN rail through an external resistor 10 kΩ. A value of 4.7 kΩ is preferred in high-noise environments. <p>If switch control is desired, no external pulldown resistors are necessary. Simply connect SPST switches directly to the VDD_SNVS_IN rail. If desired, a 4.7 kΩ to 10 kΩ series resistor can be used when current drain is critical.</p> | <p>Boot inputs BOOT_MODE1 and BOOT_MODE0 each have on-chip pulldown devices with a nominal value of 100 kΩ, a projected minimum of 60 kΩ, and a projected maximum of 140 kΩ.</p> <p>Be aware that when these are logic high, current is drawn from the VDD_SNVS supply. In production, when on-chip fuses determine the boot configuration, both boot mode inputs can be no connects</p> |

Table 2-4. I²C recommendations

| Checkbox | Recommendation | Explanation/supplemental recommendation |
|----------|--|---|
| | <p>1. Verify the target I²C interface clock rates.</p> | <p>The bus can only operate as fast as the slowest peripheral on the bus. If faster operation is required, move the slow devices to another I²C port.</p> |
| | <p>2. Verify that the target I²C address range is supported and does not conflict with other peripherals. If there is an unavoidable address conflict, move the offending device to another I²C port.</p> | <p>These chips support up to four I²C ports.</p> <p>If it is undesirable to move a conflicting device to another I²C port, review the peripheral operation to see if it supports remapping the address.</p> |
| | <p>3. Do not place more than one set of pullup resistors on the I²C lines.</p> | <p>This can result in excessive loading. Good design practice is to place one pair of pullups only.</p> |

Table 2-5. JTAG recommendations

| Checkbox | Recommendation | Explanation/supplemental recommendation |
|----------|---|---|
| | 1. Do not use external pullup or pulldown resistors on JTAG_TDO. | JTAG_TDO is configured with an on-chip keeper circuit such that the floating condition is actively eliminated if an external pull resistor is not present. An external pull resistor on JTAG_TDO is detrimental. See Table 2-15 for a summary of the JTAG interface. |
| | 2. Ensure that the on-chip pullup/pulldown configuration is followed if external resistors are used with JTAG signals (with the exception of JTAG_TDO). For example, do not use an external pulldown on an input that has an on-chip pullup. | External resistors can be used with all JTAG signals except JTAG_TDO, but they are not required. See Table 2-15 for a summary of the JTAG interface. |
| | 3. JTAG_MOD may be referred to as SJC_MOD in some documents. Both names refer to the same signal. JTAG_MOD should be externally connected to GND for normal operation in a system. Termination to GND through an external pulldown resistor is allowed. Use $\geq 4.7\text{ k}\Omega$. | When JTAG_MOD is low, the JTAG interface is configured for common software debug, adding all the system TAPs to the chain. When JTAG_MOD is high, the JTAG interface is configured to a mode compliant with the IEEE 1149.1 standard. |

Table 2-6. Power supply decoupling recommendations¹

| Checkbox | Supply | 0.22 μF (min qty) ² | 4.7 μF | 22 μF ³ | Notes |
|----------|-------------|--|-------------------|-------------------------------|---|
| | VDD_ARM_IN | 2 | | 1 | 19x19 package: Place 22 μF cap and one of the 0.22 μF caps next to the ball J21. Place "+" within 50 mils of via. 17x17WP package: Place 22 μF cap and one of the 0.22 μF caps next to the ball H18. Place "+" within 50 mils of via. 17x17NP package: Place 22 μF cap and one of the 0.22 μF caps next to the ball H18. Place "+" within 50 mils of via. 14x14 package: Place 22 μF cap and one of the 0.22 μF caps next to the ball H18. Place "+" within 50 mils of via. |
| | VDD_ARM_CAP | 4 | | 1 | 19x19 package: Place 22 μF cap and one of the 0.22 μF caps next to the ball C18. Place "+" within 50 mils of via. 17x17WP package: Place 22 μF cap and one of the 0.22 μF caps next to the ball C16. Place "+" within 50 mils of via. 17x17NP package: Place 22 μF cap and one of the 0.22 μF caps next to the ball C16. Place "+" within 50 mils of via. 14x14 package: Place 22 μF cap and one of the 0.22 μF caps next to the ball C16. Place "+" within 50 mils of via. Do not connect any loads to VDDARM_CAP. |

Table continues on the next page...

Table 2-6. Power supply decoupling recommendations¹ (continued)

| Checkbox | Supply | 0.22 uF (min qty) ² | 4.7 uF | 22 uF ³ | Notes |
|----------|---|-----------------------------------|--------|--------------------|---|
| | VDD_SOC_IN | 3 | | 1 | <p>19x19 package: Place 22 μF cap and one of the 0.22uF caps next to the ball C9. Place "+" within 50 mils of via.</p> <p>17x17WP package: Place 22 μF cap and one of the 0.22uF caps next to the ball C8. Place "+" within 50 mils of via.</p> <p>17x17NP package: Place 22 μF cap and one of the 0.22uF caps next to the ball C8. Place "+" within 50 mils of via.</p> <p>14x14 package: Place 22 μF cap and one of the 0.22uF caps next to the ball D8. Place "+" within 50 mils of via.</p> |
| | VDD_SOC_CAP | 5 | | 1 | <p>19x19 package: Place 22 μF cap and one of the 0.22uF caps next to the ball AA10. Place "+" within 50 mils of via.</p> <p>17x17WP package: Place 22 μF cap and one of the 0.22uF caps next to the ball V8. Place "+" within 50 mils of via.</p> <p>17x17NP package: Place 22 μF cap and one of the 0.22uF caps next to the ball V8. Place "+" within 50 mils of via.</p> <p>14x14 package: Place 22 μF cap and one of the 0.22uF caps next to the ball V8. Place "+" within 50 mils of via.</p> <p>VDDSOC_CAP is restricted to MX6 loads.</p> |
| | VDD_HIGH_IN | 1 | 1 | | |
| | VDD_HIGH_CAP | 1 | 1 | | VDDHIGH_CAP is restricted to MX6 loads. |
| | VDD_SNVS_IN | | | | |
| | VDD_SNVS_CAP | 1 | | | <p>If the nominal value is larger than recommended, power-up/down ramp time is excessive and suspend/resume operation cannot be guaranteed. Select a small capacitor with low ESR.</p> <p>Do not connect any loads to VDD_SNVS_CAP.</p> |
| | PCIE_VP or PCIE_VPTX (19x19 package) | | 1 | | Place capacitors as close to the ball as possible. |
| | PCIE_VP or PCIE_VPTX (17x17 WP package) | | 1 | | Place capacitors as close to the ball as possible. |
| | PCIE_VP_CAP (17x17 NP package) | | 1 | | Place capacitors as close to the ball as possible. |
| | PCIE_VP_CAP (14x14 package) | | 1 | | Place capacitors as close to the ball as possible. |
| | NVCC_DRAM | 4 | | 1 | Can be separated into four 4.7uF caps instead of single 22 μ F |

Table continues on the next page...

Table 2-6. Power supply decoupling recommendations¹ (continued)

| Checkbox | Supply | 0.22 μ F (min qty) ² | 4.7 μ F | 22 μ F ³ | Notes |
|----------|----------------------|--|-------------|-------------------------|--|
| | NVCC_PLL | 1 | 1 | | Do not connect any loads to this LDO output. |
| | NVCC_xxxx | 1 per via | | | One capacitor per via. Grouped NVCC balls can share a capacitor. |
| | VDD_USB_CAP | 1 | 2 | | May use a single 10 μ F capacitor instead of 2 4.7 μ F capacitors. Do not connect any loads to this LDO output. |
| | USB_OTG1_VBUS | 1 | 1 | | 16V rated |
| | USB_OTG2_VBUS | 1 | 1 | | 16V rated |
| | NVCC_USB_H (1.2V) | 1 | 1 | | — |

1. Use the smallest capacitor package size allowed with your design rules.
2. For 0.22 μ F capacitors, use 0402 package.
3. For 22 μ F capacitors, 0603 package preferred; 0805 and 1206 are acceptable.

Table 2-7. Power and decoupling recommendations

| Checkbox | Recommendation | Explanation/supplemental recommendation |
|----------|--|--|
| | 1. Comply with the power-up sequence guidelines as described in the data sheet to guarantee reliable operation of the device. | Any deviation from these sequences may result in the following situations: <ul style="list-style-type: none"> • Excessive current during power-up phase • Prevention of the device from booting • Irreversible damage to the processor (worst-case scenario) |
| | 2. Do not overload coin cell backup power rail VDD_SNVS_IN. Note that the following I/Os are associated with VDD_SNVS_IN; most inputs have on-chip pull resistors and do not require external resistors: <ul style="list-style-type: none"> • POR_B – on-chip pullup • ONOFF – on-chip pullup • BOOT_MODE0 – on-chip pulldown • BOOT_MODE1 – on-chip pulldown • TAMPER – on-chip pulldown • PMIC_STBY_REQ – push-pull output • PMIC_ON_REQ – push-pull output • TEST_MODE – on-chip pulldown | NXP PMIC PMPF0100 VSNVS regulator is rated to supply 400 μ A output current under worst-case operating conditions. The VDD_SNVS_IN regulator can supply larger current in transient situations without damaging the regulator. Concerning i.MX6: <ul style="list-style-type: none"> • When VDD_SNVS_IN = VDD_HIGH_IN, SNVS domain current is drawn from both equally. • When VDD_HIGH_IN > VDD_SNVS_IN, VDD_HIGH_IN supplies all SNVS domain current and current flows into VDD_SNVS_IN to charge a coin cell battery. • When VDD_SNVS_IN > VDD_HIGH_IN, VDD_SNVS_IN supplies current to SNVS, and some current flows into VDD_HIGH_IN. <p>Note: VDD_HIGH_IN must be valid (above the internal detector threshold, 2.4 V typ) for the current flow to occur. Thus, current flow only happens when VDD_HIGH_IN is powered to a level below VDD_SNVS_IN. If VDD_HIGH_IN is off or low, no extra current is drawn from VDD_SNVS_IN. The whole circuit assumes it is charging a coin cell and starts charging when VDD_HIGH_IN is valid. If you are driving</p> |

Table continues on the next page...

Table 2-7. Power and decoupling recommendations (continued)

| | | |
|--|--|--|
| | | <p>VDD_SNVS_IN with a non-battery power source, it must be at the same level as VDD_HIGH_IN or current will flow between them.</p> <ul style="list-style-type: none"> When VDD_SNVS_IN is not powered by a battery, it is recommended that VDD_SNVS_IN = VDD_HIGH_IN. If VDD_SNVS_IN is tied to a battery, the battery eventually discharges to a value equal to that of VDD_HIGH_IN and never subsequently charges above VDD_HIGH_IN. <p>The battery chemistry may add restrictions to VDD_HIGH_IN's voltage range. External charging components should be based on the battery manufacturer's specifications.</p> |
| | 3. Maximum ripple voltage requirements. | <p>Common requirement for ripple noise should be less than 5% Vp-p of supply voltage average value.</p> <p>Related power rails affected: all VDD_xxx_IN and VDD_xxx_CAP.</p> |
| | 4. NVCC_LVDS must be powered-on even when not using the LVDS interface. | <p>The DDR pre-drivers share the NVCC_LVDS power rail with the LVDS interface. VDDHIGH_CAP can be utilized as the power source; tie NVCC_LVDS to VDDHIGH_CAP.</p> |
| | <p>5. If VDD_SNVS_IN is directly supplied by a coin cell, a schottky diode is required between VDD_HIGH_IN and VDD_SNVS_IN. The cathode is connected to VDD_SNVS_IN.</p> <p>Alternately, VDD_HIGH_IN and VDD_SNVS_IN can be tied together if the real-time clock function is not needed during system power-down.</p> | <p>When no power is supplied to VDD_VSNVS_IN, the diode limits the voltage difference between the two on-chip SNVS power domains to approximately 0.3 V. The processor is designed to allow current flow between the two SNVS power domains proportional to the voltage difference.</p> |
| | <p>6. If boundary scan test (BSDL) will be used, the following supplies must be powered: PCIE_VP, PCIE_VPH, PCIE_VPTX</p> | <p>The boundary scan test scan chain runs through the PCIe PHY. If the PCIe PHY supplies are not powered, the scan chain will not function.</p> <p>The PCIe supply connections present depend on the package.</p> <p>PCIE_VP, PCIE_VPTX and PCIE_VP_CAP are internally connected to the output of the LDO_PCIE. LDO_PCIE must be enabled for boundary scan to function. LDO_PCIE is enabled at reset.</p> <p>PCIE_VPH is a supply input and must be powered for boundary scan to function. On the 17x17 NP package, PCIE_VPH is connected to VDD_HIGH_CAP inside the package so it does not need to be supplied externally.</p> |

Table 2-8. Oscillator and clock recommendations

| Checkbox | Recommendation | Explanation/supplemental recommendation |
|----------|---|---|
| | 1. Precision 32.768 kHz oscillator | <p>The capacitors implemented on either side of the crystal are about twice the crystal load capacitance. To hit the target oscillation frequency, board capacitors need to be reduced to compensate for board and chip</p> |

Table continues on the next page...

Table 2-8. Oscillator and clock recommendations (continued)

| | | |
|--|---|--|
| | <p>Connect a crystal between RTC_XTALI and RTC_XTALO. Choose a crystal with a maximum of 100 kΩ ESR (equivalent series resistance) and follow the manufacturer's recommendation for loading capacitance.</p> <p>Do not use an external biasing resistor because the bias circuit is on-chip.</p> | <p>parasitic capacitance; typically 15–16 pF is employed. The integrated oscillation amplifier has an on-chip self-biasing scheme, but is high-impedance (relatively weak) to minimize power consumption. Care must be taken to limit parasitic leakage from RTC_XTALI and RTC_XTALO to either power or ground (> 100 MΩ) as this negatively affects the amplifier bias and causes a reduction of startup margin.</p> <p>Use short traces between the crystal and the processor, with a ground plane under the crystal, load capacitors, and associated traces.</p> |
| | <p>2. External kilohertz source</p> <p>If feeding an external clock into the device, RTC_XTALI can be driven DC-coupled with RTC_XTALO floated or driven with a complimentary signal.</p> | <p>The voltage level of this driving clock should not exceed the voltage of VDD_SNVS_CAP and the frequency should be <100 kHz under typical conditions. Do not exceed VDD_SNVS_CAP or damage/malfunction may occur. The RTC_XTALI signal should not be driven if the VDD_SNVS_CAP supply is off. This can lead to damage or malfunction. For RTC_XTALI VIL and VIH voltage levels, see the latest i.MX 6 series datasheet available at www.nxp.com.</p> <p>Note that if this external clock is stopped, the internal ring oscillator starts automatically.</p> |
| | <p>3. Loose-tolerance 40 kHz oscillator</p> <p>An on-chip loose-tolerance ring oscillator is available of approximately 40 kHz. If RTC_XTALI is tied to GND and RTC_XTALO is floating, the on-chip oscillator is automatically engaged.</p> | <p>When a high-accuracy real-time clock is not required, the system may use the on-chip 40 kHz oscillator. The tolerance is $\pm 50\%$.</p> <p>The ring oscillator starts faster than an external crystal and is used until the external crystal reaches stable oscillation. The ring oscillator also starts automatically if no clock is detected at RTC_XTALI at any time.</p> |
| | <p>4. Precision 24 MHz oscillator</p> <p>Connect a fundamental-mode crystal between XTALI and XTALO. An 80 Ω typical ESR crystal rated for a maximum drive level of 250 μW is acceptable.</p> <p>Alternately, a 50 Ω typical ESR crystal rated for a maximum drive level of 200 μW may be used. See the engineering bulletin EB830 on www.nxp.com for additional options.</p> | <p>NXP BSP software requires 24 MHz on this clock. This clock is used as a reference for USB and PCIe, so there are strict frequency tolerance and jitter requirements. See Table 2-16 for guidelines. See the crystal oscillator (XTALOSC) reference manual chapter and relevant interface specification chapters for details.</p> <p>To access a calculator for the 24 MHz crystal drive level, see EB830 on the i.MX Community.</p> |
| | <p>5. External megahertz source</p> <p>If feeding an external clock into the device, XTALI can be driven DC-coupled with XTALO floated.</p> | <p>For XTALI VIL and VIH voltage levels, see the latest i.MX 6 series datasheet. This clock is used as a reference for USB and PCIe, so there are strict frequency tolerance and jitter requirements. See Table 2-16 for guidelines. See the crystal oscillator (XTALOSC) reference manual chapter and relevant interface specification chapters for details.</p> |
| | <p>6. CCM_LK1_P/ CCM_CLK1_N are LVDS input/output differential pairs compatible with TIA/EIA-644 standard. The frequency range is 0 to 600 MHz.</p> <p>Alternatively, a single-ended signal can be used to drive a CCM_CLKx_P input. In this case, the corresponding CCM_CLKx_N input should be tied to a</p> | <p>The clock inputs/outputs are general-purpose differential high-speed clock Input/outputs.</p> <p>Any or both of them can be configured:</p> <ul style="list-style-type: none"> As inputs to feed external reference clocks to the on-chip PLLs and/or modules, for example as alternate reference clock for PCIe video/audio interfaces. |

Table continues on the next page...

Table 2-8. Oscillator and clock recommendations (continued)

| | | |
|--|--|---|
| | <p>constant voltage level equal to 50% of VDD_HIGH_CAP. Termination should be provided with high-frequency signals.</p> <p>See the LVDS pad electrical specification in the data sheet for further details.</p> <p>After initialization, the CCM_CLKx inputs/outputs can be disabled (if not used) by the PMU_MISC1 register. If unused, any or both of the CCM_CLKx_N/P pairs may be left floating.</p> | <ul style="list-style-type: none"> As outputs to be used as either a reference clock or as a functional clock for peripherals, for example an output of the PCIe master clock (root complex use). See the chip reference manual for details on the respective clock trees. |
| | <p>7. Bias XTALI with a 2.2 MΩ resistor to GND. Mount the resistor close to the XTALI ball.</p> | <p>The XTALI bias must be adjusted externally to ensure reasonable start-up time.</p> |

Table 2-9. Reset and ONOFF recommendations

| Checkbox | Recommendation | Explanation/supplemental recommendation |
|----------|--|---|
| | <p>1. If the external SRC_POR_B signal is used to control the processor POR, then SRC_POR_B must be immediately asserted at power-up and remain asserted until the VDD_ARM_CAP and VDD_SOC_CAP supplies are stable. VDD_ARM_IN and VDD_SOC_IN may be applied in either order with no restrictions. In the absence of an external reset feeding the SRC_POR_B input, the internal POR module takes control.</p> | <p>A reset switch may be wired to the chip's POR_B, which is a cold-reset negative-logic input that resets all modules and logic in the IC. POR_B may be used in addition to internally generated power-on reset signal (logical AND, both internal and external signals are considered active low).</p> |
| | <p>2. For portable applications, the ONOFF input may be connected to an ON/OFF SPST push-button switch. On-chip debouncing is provided, and this input has an on-chip pullup. If not used, ONOFF should be a no connect.</p> | <p>A brief connection to GND in OFF mode causes the internal power management state machine to change state to ON.</p> <p>In ON mode, a brief connection to GND generates an interrupt (intended to be a software-controllable power-down).</p> <p>An approximate 5 second or more connection to GND causes a forced OFF.</p> |

Table 2-10. PCIe recommendations

| Checkbox | Recommendation | Explanation/supplemental recommendation |
|----------|---|--|
| | <p>1. Termination is required on the differential clock lines. Connect two 49.9 Ω resistors, one between REFCLK- and GND, the other between REFCLK+ and GND. Alternately, Connect a 100 Ω resistor between REFCLK- and REFCLK+.</p> | <p>These termination resistors should be placed as close as possible to the receiver device inputs in case the chip LVDS clock outputs are used as the REFCLK source for the PCIe endpoint device.</p> |
| | <p>2. The differential transmitter must be ac coupled. Use a 0.1 μF-series capacitor on PCIE_TX_P and a second 0.1 μF on PCIE_TX_M.</p> | <p>To ensure PCIe specification compliance, ac coupling is required at each transmitter. The receiver must be dc coupled.</p> |
| | <p>3. PCIe Jitter compliance</p> <p>NXP recommends including an external clock source that meets the PCIe jitter specification until the i.MX 6SoloX PCIe jitter compliance can be assessed.</p> | <p>On previous i.MX6 SoCs, the on-chip PCIe clock generation did not meet the jitter requirements of the PCIe specification. This has not yet been evaluated on the i.MX 6SoloX.</p> |

Table 2-11. USB recommendations

| Checkbox | Recommendation | Explanation/supplemental recommendation |
|----------|--|---|
| | 1. USB OTG To comply with the USB OTG specification, the VBUS supply on the OTG connector should default to <i>off</i> when the boards power up. | The processor should turn VBUS <i>on</i> as required. |
| | 2. USB Host USB_H1_VBUS should be directly connected to a 5 V supply. | Tie USB_H1_VBUS to an unswitched 5 V supply for the typical use case. However, if the system is a USB device, then USB_H1_VBUS may be a no connect. |
| | 3. USB HSIC supply For USB, HSIC operation, the NVCC_USB_H supply should be configured for a nominal operating voltage of 1.2V (see the datasheet Operating Ranges table details). | If USB_H_DATA and USB_H_STROBE are used as GPIOs, they can be configured for voltages up to 2.5V nominal (see the datasheet Operating Ranges table details). NVCC_USB_H should be grounded through a 10k resistor if the HSIC pins are not used. |

Table 2-12. Reference resistor recommendations

| Checkbox | Recommendation | Explanation/supplemental recommendation |
|----------|--|--|
| | 1. PCIE_REXT – Connect an external 200 Ω 1% resistor to GND. | The impedance calibration process requires connection of this reference resistor. If PCIe is unused, the reference resistor may be populated if desired for manufacturability purposes, or left no-connect for cost savings. |

Table 2-13. Miscellaneous recommendations

| Checkbox | Recommendation | Explanation/supplemental recommendation |
|----------|--|--|
| | 1. The TEST_MODE input is internally connected to an on-chip pulldown device. The user can either float this signal or tie it to GND. | This input is reserved for NXP manufacturing use. |
| | 2. For termination of unused analog interfaces, see Table 2-17 | — |
| | 3. GPANAIO must be a no connect. | This output is reserved for NXP manufacturing use. |
| | 4. NC contacts are no connect and should be floated. | Depending on the feature set, some versions of the IC may have NC contacts connected inside the BGA. |

2.3 Bus isolation circuit

The following figure provides supporting information for [Table 2-2](#), recommendation #1.

Boot Select

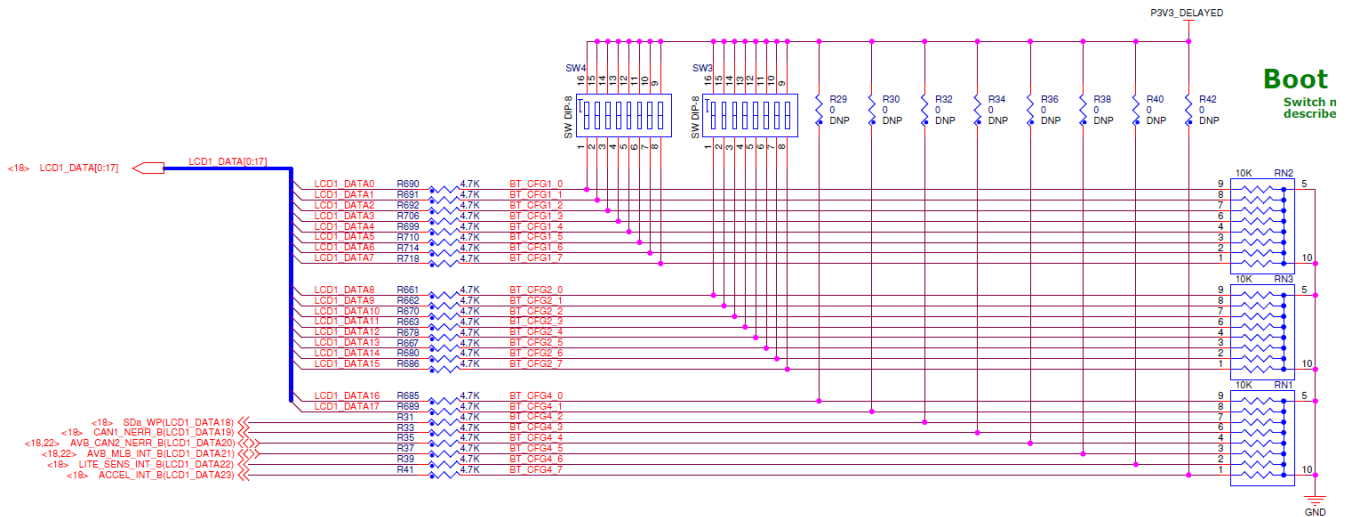


Figure 2-1. Boot configuration for development mode

2.4 DDR reference circuit

The following table is a resistor chart (see [Table 2-1](#), recommendation #2). The recommendations are appropriate for designs with DDR memory chips with a maximum Vref input current of 2 μ A each.

Table 2-14. DDR Vref resistor sizing guideline

| Number of DRAM with 2 μ A Vref input current | Resistor divider value (2 resistors) |
|--|---|
| 2 | $\leq 1.21 \text{ k}\Omega \text{ 1\%}$ |
| 2 | $\leq 1.54 \text{ k}\Omega \text{ 0.5\%}$ |
| 2 | $\leq 2.32 \text{ k}\Omega \text{ 0.1\%}$ |

2.5 JTAG signal termination

The following table is a JTAG termination chart (see recommendations in [Table 2-5](#)).

Table 2-15. JTAG interface summary

| JTAG signal | I/O type | On-chip termination | External termination |
|-------------|----------|----------------------|---|
| JTAG_TCK | Input | 47 k Ω pullup | Not required; can use 10 k Ω pullup |
| JTAG_TMS | Input | 47 k Ω pullup | Not required; |

Table continues on the next page...

Table 2-15. JTAG interface summary (continued)

| | | | |
|------------|----------------|-----------------------|---|
| | | | can use 10 k Ω pullup |
| JTAG_TDI | Input | 47 k Ω pullup | Not required; can use 10 k Ω pullup |
| JTAG_TDO | 3-state output | Keeper | <u>Do not</u> use pullup or pulldown |
| JTAG_TRSTB | Input | 47 k Ω pullup | Not required; can use 10 k Ω pullup |
| JTAG_MOD | Input | 100 k Ω pullup | Use 1 k Ω pulldown or tie to GND |

2.6 Oscillator tolerance

The following table provides 24 MHz oscillator tolerance guidelines (see [Table 2-8](#), recommendations #4 and #5). Because these are guidelines, the designer must verify all tolerances per the official specifications.

Table 2-16. 24 MHz crystal tolerance guidelines

| Interface | Tolerance (\pm ppm) |
|-----------|------------------------|
| Ethernet | 50 |
| USB2.0 | 150 |
| PCIe | 300 |

2.7 Unused analog interfaces

[Table 2-17](#) shows the recommended connections for unused analog interfaces (see [Table 2-13](#), recommendation #2).

Table 2-17. Recommended connections for unused analog interfaces

| Module | Contact name | Recommendations if unused |
|--------|--|---|
| ADC | ADC1_IN[3:0], ADC2_IN[3:0] | Float |
| | ADC_VREFL | Ground |
| | ADC_VREFH | Tie to VDDA_ADC_3P3 |
| | VDDA_ADC_3P3 | VDDA_ADC_3P3 must be powered even if the ADC is not used. |
| CCM | CCM_CLK1_P, CCM_CLK1_N, CCM_CLK2 | Float |
| LDB | LVDS_CLK_P, LVDS_CLK_N LVDS_DATA0_P, LVDS_DATA0_N | Float |

Table continues on the next page...

Table 2-17. Recommended connections for unused analog interfaces (continued)

| | | |
|---------|--|--|
| | LVDS_DATA1_P, LVDS_DATA1_N LVDS_DATA2_P, LVDS_DATA2_N LVDS_DATA3_P, LVDS_DATA3_N | |
| PCIe | PCIE_REXT, PCIE_RX_N, PCIE_RX_P, PCIE_TX_N, PCIE_TX_P | Float |
| | PCIE_VP, PCIE_VPTX, PCIE_VP_CAP | 4.7 μ F capacitor to ground ¹ |
| | PCIE_VPH | Float or ground ¹ |
| RTC | RTC_XTALI | Ground |
| | RTC_XTALO | Float |
| USB OTG | USB_OTG1_CHD_B, USB_OTG1_DN, USB_OTG1_DP, USB_OTG1_VBUS USB_OTG2_CHD_B, USB_OTG2_DN, USB_OTG2_DP, USB2_OTG_VBUS | Float |

1. These supplies must remain powered if boundary scan test needs to be done. Since the internal LDO_PCIE is enabled after reset, the application may disable the LDO by setting the register field PMU_REG_CORE[REG1_TARG] = "0000" (power gated off).

Chapter 3

i.MX 6 Series Layout Recommendations

3.1 Introduction

This chapter provides recommendations to assist design engineers with the layout of an i.MX 6 series-based system.

3.2 Basic design recommendations

The i.MX 6SoloX processor comes in multiple packages. For detailed information, see the i.MX 6.

When using the Allegro tool, optimal practice is to use the footprint as created by NXP. When not using the Allegro tool, use the Allegro footprint export feature (supported by many tools). If export is not possible, create the footprint per the package mechanical dimensions outlined in the product data sheet.

Native Allegro layout and gerber files are available on www.nxp.com.

3.2.1 Placing decoupling capacitors

Place small decoupling and larger bulk capacitors on the bottom side of the PCB.

The 0201 decoupling and 0603 bulk capacitors should be mounted as close as possible to the power vias. The distance should be less than 50 mils. Additional bulk capacitors can be placed near the edge of the BGA via array. Placing the decoupling capacitors close to the power balls is critical to minimize inductance and ensure high-speed transient current demand by the processor.

A correct via size is critical for preserving adequate routing space. The recommended geometry for the via pads is: pad size 18 mils and drill 8 mils.

The following list provides the main recommendations for choosing the correct decoupling scheme:

- Place the largest capacitance in the smallest package that budget and manufacturing can support.
- For high speed bypassing, select the required capacitance with the smallest package (for example, 0.22 μ F and package 0201).
- Minimize trace length (inductance) to small caps.
- Series inductance cancels out capacitance.
- Tie caps to GND plane directly with a via.
- Place capacitors close to the power contact of the associate package designed from the schematic.

A preferred BGA power decoupling design is the layout is available through www.nxp.com. Customers should use the NXP design strategy for power and decoupling.

3.3 Stackup recommendations

High-speed design requires a good stackup in order have the right impedance for the critical traces. The constraints for the trace width may depend on a number of factors, such as the board stackup and associated dielectric and copper thickness, required impedance, and required current (for power traces). The NXP reference design uses a minimum trace width of 3 mils for the DDR routing. The stackup also determines the constraints for routing and spacing.

Consider the following when designing the stackup and selecting the material for your board.

- Board stack-up is critical for high-speed signal quality.
- You must preplan impedance of critical traces
- High-speed signals must have reference planes on adjacent layers to minimize cross-talk.
- FSL reference design equals Isola 370HR.
- FSL validation boards equals Isola FR408.

The recommended stackup is 8-layers, with the layer stack as shown in the following table. The lefthand image shows the detail provided by NXP inside the fabrication detail as a part of the Gerber files. The righthand side shows the solution suggested by the PCB fabrication company for our requirements.

Table 3-1. SABRE SD board layer stack

| Layer | Layer type | Finished copper weight |
|-------|------------|------------------------|
|-------|------------|------------------------|

Table continues on the next page...

Table 3-1. SABRE SD board layer stack (continued)

| | | |
|---|----------------------|---------|
| 1 | Signal – top side | 3/8 oz. |
| 2 | Ground plane | 1/2 oz. |
| 3 | Signal – Internal 1 | 1/2 oz. |
| 4 | Power 1 | 1/2 oz. |
| 5 | Power 2 | 1/2 oz. |
| 6 | Signal – Internal 2 | 1/2 oz. |
| 7 | Ground plane | 1/2 oz. |
| 8 | Signal – bottom side | 3/8 oz. |

The following table shows a working stack-up implementation:

Table 3-2. Stackup implementation

| Layers | Single ended | | Differential | | | | | |
|--------|--------------------|-------------------------|--------------------|-------------------------------|-------------------------|--------------------|-------------------------------|-------------------------|
| | Trace width (Mils) | Impedance (Ω s) | Trace width (Mils) | Trace spacing 'Airgap' (Mils) | Impedance (Ω s) | Trace width (Mils) | Trace spacing 'Airgap' (Mils) | Impedance (Ω s) |
| TOP | 4.7 | 50 | 4.3 | 5.7 | 90 | 3.7 | 5.3 | 100 |
| INT1 | 4.5 | 50 | 4.2 | 5.8 | 90 | 3.8 | 5.2 | |
| INT2 | 4.5 | 50 | 4.2 | 5.8 | 90 | 3.8 | 5.2 | |
| BOT | 4.7 | 50 | 4.3 | 5.7 | 90 | 3.7 | 5.3 | 100 |




| Impedance Type | Layer | Design | Actual | Pitch | Plane | Target | Tol (ohms) | Predict |
|---|-------|---------|--------|--------|-------|--------|------------|---------|
| 1  Surface MS | L1 | 0.00470 | 0.0047 | - | - | 50 | 5.0 | 49.96 |
| | - | - | - | - | L2 | | | |
| 2  EC Microstrip | L1 | - | 0.0043 | 0.0100 | - | 90 | 9.0 | 90.62 |
| | - | - | 0.0043 | - | L2 | | | |
| 3  EC Microstrip | L1 | 0.00370 | 0.0034 | 0.0090 | - | 100 | 10.0 | 98.88 |
| | - | 0.00370 | 0.0034 | - | L2 | | | |

Figure 3-1. Example top layer impedance solution from PCB fabricator

3.4 DDR connection information

The following figures show the block diagrams from the reference design boards for the DDR3 interface and the LPDDR2 interface (respectively) with the i.MX 6SX.

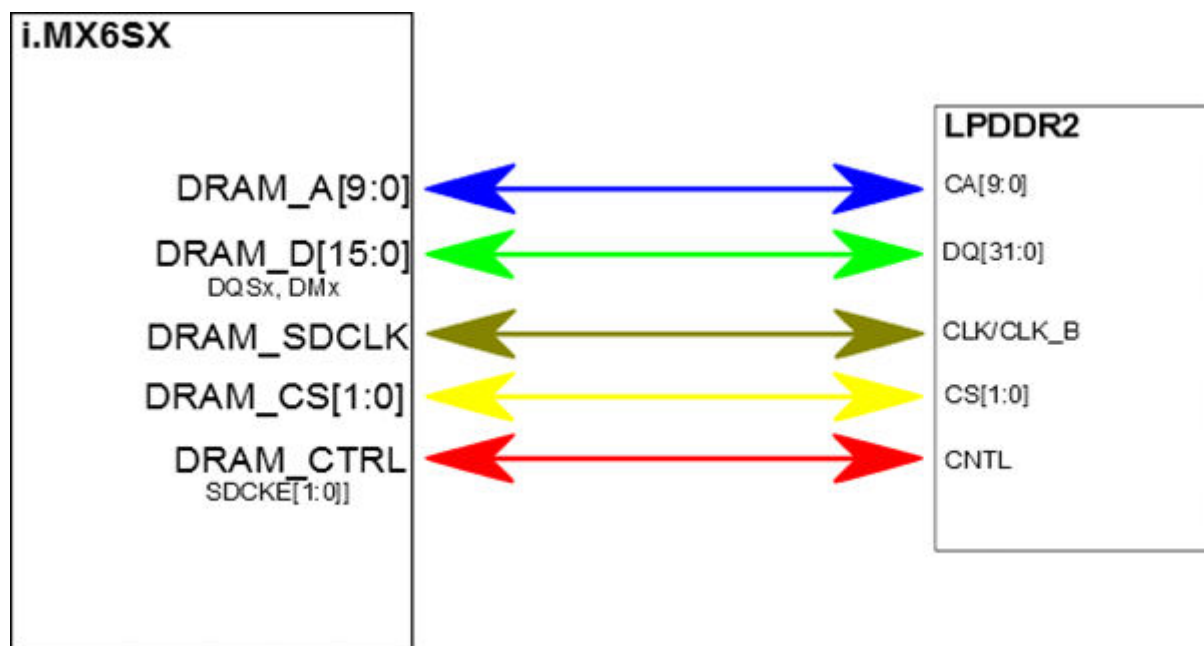


Figure 3-2. Connection between i.MX 6SX and LPDDR2

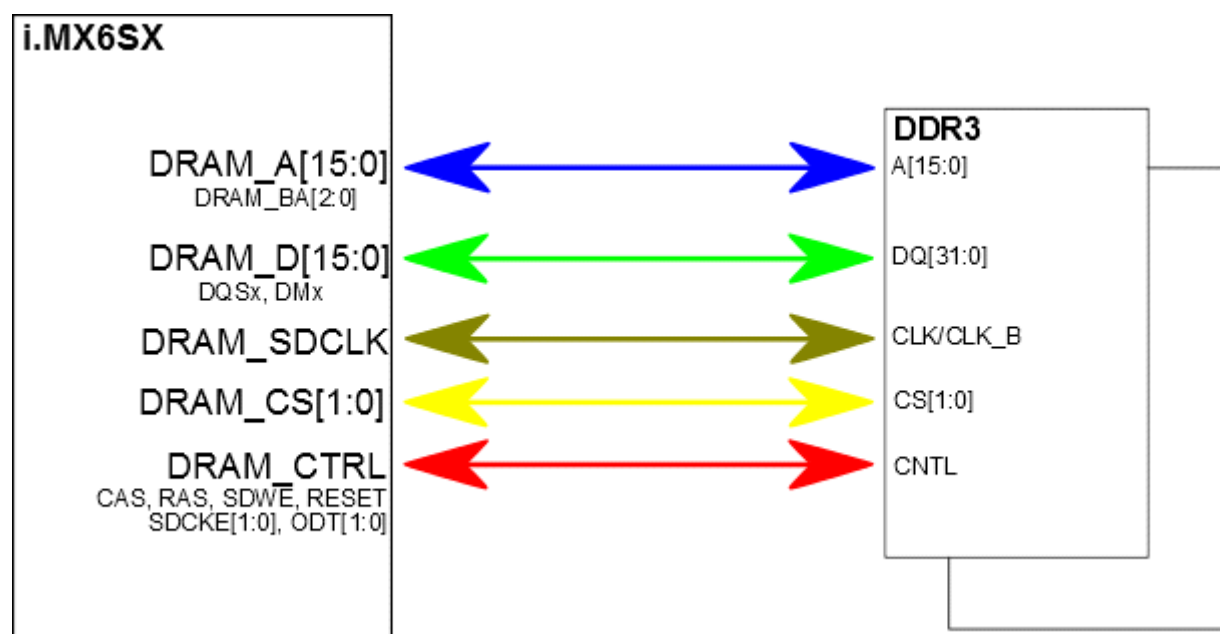


Figure 3-3. Connection between i.MX 6SX and DDR3

The DDR3 interface is one of the most critical interfaces for chip routing. It must have the controlled impedance for the single ended traces be equal to 50 Ω and for the differential pairs be equal to 100 Ω .

The following figure shows the physical connection scheme for both top and bottom placement of the DDR chips, showing the final placement of the DDR3 memory and the decoupling capacitors. The blue figure shows the top layer and the red figure shows the

bottom layer. It is very important to place the memory as close to the processor as possible to reduce trace capacitance and keep the propagation delay to the minimum. Follow the reference board layout as a guideline for memory placement and routing.

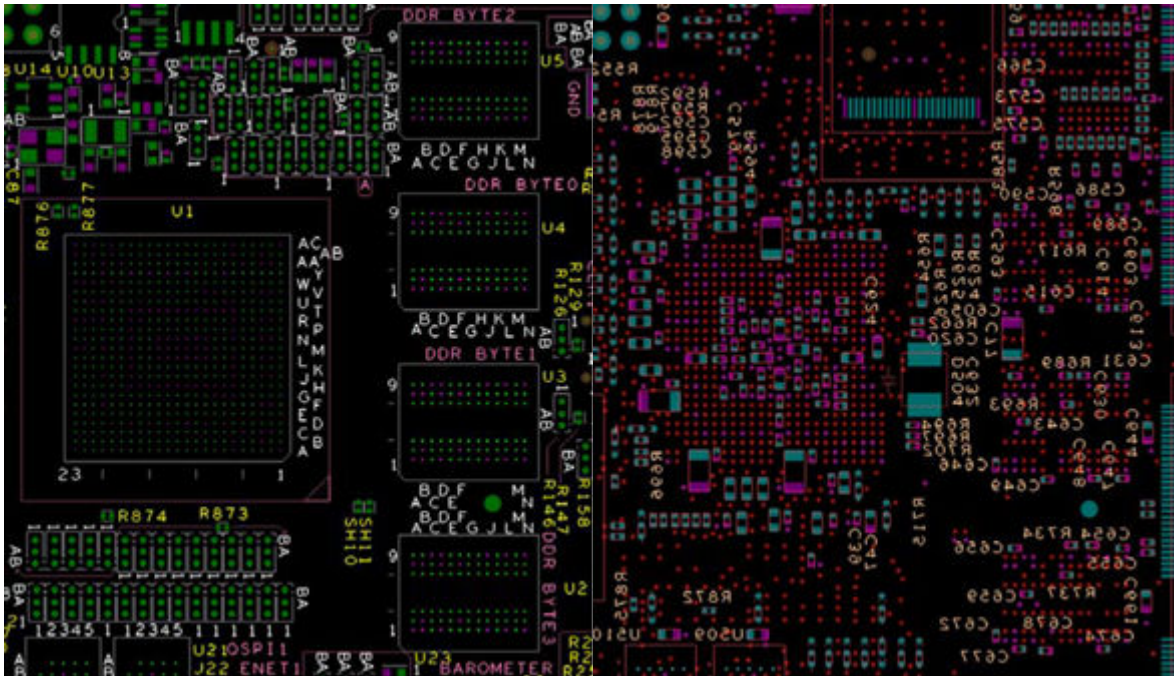


Figure 3-4. Final placement of memories and decoupling capacitors

3.4.1 DDR routing rules

DDR3 routing can be accomplished in two different ways: routing all signals at the same length or routing by byte group.

Routing all signals at the same length can be more difficult at first because of the tight space between the DDR and the processor and the large number of required interconnects. However, it is the better way because it makes signal timing analysis straightforward. Ideally, we could route all the signals at the same length. Nevertheless, it could be difficult because of the large number of connections in the tight space between the DDR and the processor. The following table explains the rules for routing the signals by the same length.

Table 3-3. DDR3 routing by the same length Signals Total length Recommendations

| Signals | Total length | Recommendations |
|------------------|--------------|---|
| Address and Bank | Clock length | Match the signals ± 25 mils of the value specified in the length column |
| Data and Buffer | Clock length | Match the signals ± 25 mils of the value specified in the length column |

Table continues on the next page...

Table 3-3. DDR3 routing by the same length Signals Total length Recommendations (continued)

| | | |
|--|-------------------------------|---|
| Control signals | Clock length | Match the signals ± 25 mils of the value specified in the length column |
| Clock DRAM_SDCLK[1:0] | Longest trace ≤ 3 inches | Match the signals of clocks signals ± 5 mils. Each differential clock pair |
| DRAM_SDQS[4:0] and DRAM_SDQS[4:0]_B | Clock length | Match the signals of DQS signals ± 10 mils of the value specified in the length column. |

Routing by byte group requires better control of the signals of each group. It is also more difficult for analysis and constraint settings. However, its advantage is that the constraint to match lengths can be applied to a smaller group of signals. This is often more achievable once the constraints are properly set. The following table explains the rules for routing the signals by byte group.

Table 3-4. DDR3 routing by byte group

| Chip signals | Group | Length (mils) | | Recommendations |
|---|---------------------|-------------------|--------------------------|---|
| | | Min | Max | |
| DRAM_SDCLK[1:0] DRAM_SDCLK_B[1:0] | Clock | Short as possible | 2.25 inches | Match the signals ± 5 mils. 2.25 inches is recommended. |
| DRAM_A[15:0] DRAM_SDBA[2:0] DRAM_RAS DRAM_CAS DRAM_SDWE | Address and Command | Clock (min) – 200 | Clock (min) ¹ | Match the signals ± 25 mils. |
| DRAM_D[7:0] DRAM_DQM0 DRAM_SDQS0 DRAM_SDQS0_B | Byte Group 1 | — | Clock (min) | Match the signals of each byte group ± 25 mils. Match the differential signals of DQS ± 10 mils. |
| DRAM_D[15:8] DRAM_DQM1 DRAM_SDQS1 DRAM_SDQS1_B | Byte Group 2 | — | Clock (min) | |
| DRAM_D[23:16] DRAM_DQM2 DRAM_SDQS2 DRAM_SDQS2_B | Byte Group 3 | — | Clock (min) | |
| DRAM_D[31:24] DRAM_DQM3 DRAM_SDQS3 DRAM_SDQS3_B | Byte Group 4 | — | Clock (min) | |
| DRAM_CS[1:0] DRAM_SDCKE[1:0] DRAM_SDOdT[1:0] | Control signals | Clock (min) – 200 | Clock (min) | Match the signals ± 50 mils. |

1. Clock (min) — The shortest length of the clock group signals because this group has a ± 5 mil matching tolerance.

Finally, the impedance for the signals should be 50 Ω for single ended and 100 Ω for differential pairs.

3.5 Routing considerations

The chip can support up to 4 Gbytes of DRAM memory. i.MX 6SoloX DDR routing needs to be separated into three groups: data, address, and control. Each group has its own method of routing from an i.MX 6 series chip to DDR memory. The DDR layout has 2 Gbyte and 4 Gbyte options.

3.5.1 Swapping data lines

The DDR3 pin swapping technique for the data bus lines within bytes makes it easier to:

- Route direct lines
- Avoid changes between layers

The rules are as follows:

- Hardware write leveling – lowest order bit within byte lane must remain on lowest order bit of lane by JEDEC compliance (see the ‘Write Leveling’ section in JESD79-3E)
 - D0, D8, D16, and D24 are fixed
 - Other data lines free to swap within byte lane
- JEDEC DDR3 memory restrictions are:
 - No restrictions for complete byte lane swapping
 - DQS and DQM must follow lanes

NOTE

If byte lane swapping was done, target DDR IC register read value must be transposed according to the data line swapping.

3.5.2 DDR3 (32 bits) T topology considerations

Take into account the following when designing a T-topology system.

- Follow the routing rules described in [Table 3-3](#).
- Termination resistors not required.
- Short routing lengths and on-chip drive strength control.

- Your design is limited to 4 DDR chips.
- DDR3, 2 GBytes using latest memories (4 GBytes coming).

3.5.3 DDR3 (32 bits) Fly-by topology considerations

Take in to account the following recommendations when designing a Fly-by topology system

- DDR controller provides address mirroring when using two chip selects, which aids address line routing for memories on both sides of board.
- Bus termination resistors are required.

3.5.4 2-Gigabyte recommendations: T topology

The 2 Gbyte option has two memories. You should follow these recommendations for best practice:

- Have a balanced routing for the T connection.
- Avoid having many layer transitions.
- Do not cross split reference planes during the routing.

The following figure shows the topology for the ADDR/CMD/CTRL signals. It has a tree topology. Note the balanced T routing.

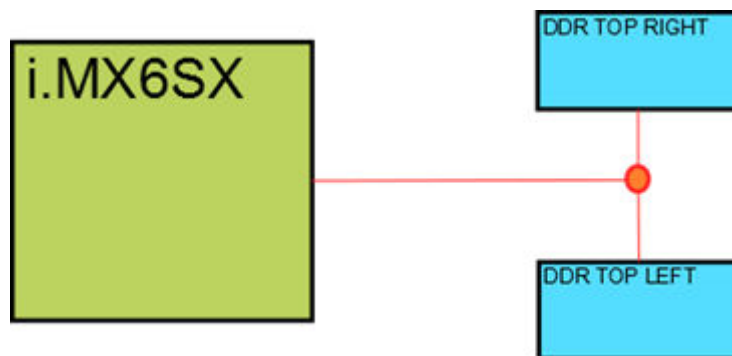


Figure 3-5. ADDR/CMD/CTRL signal topology

The following figure shows the point-to-point data bus connection, with routing by byte group.

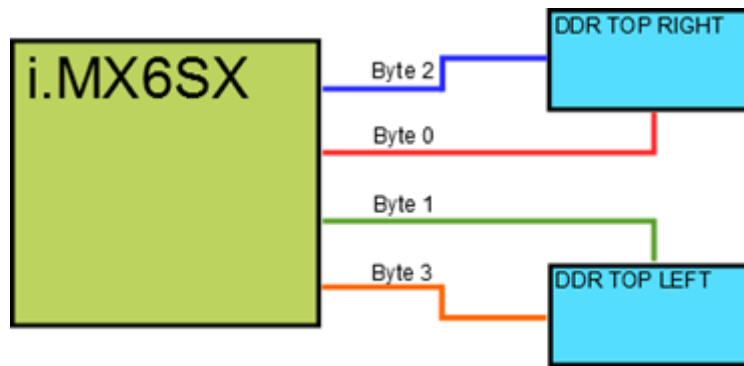


Figure 3-6. Point-to-point data bus connection (routing by byte group)

3.5.5 2-Gigabyte recommendations: Fly-by topology

The following diagrams show the 2 Gbyte recommendations using both chip selects (CS[1:0]) and loading 1 GBytes to each one. This option has four memories and requires the addition of a termination resistor.

NOTE

The fly-by examples in this guide can be used for either a one-chip select solution using 16 address traces or a two-chip select solution using only 15 address traces. The unnecessary trace may simply be deleted from the design.

Route the ADDR/CMD signals as shown in the following figure:



Figure 3-7. ADDR/CMD/CTRL signal topology

Route the Byte lane signals as shown in the following figure:



Figure 3-8. Data bus routing topology

Route the Clock differential signals as shown in the following figure:



Figure 3-9. Clock routing topology

3.5.6 Two chip T topology routing examples

The figures in this section show examples for the routing of the 2GByte DDR3 memories. The following figures are a guideline of the T configuration routing with eight layers PCB. The following table shows the color coding used in the figures.

Table 3-5. Color code

| Color | Meaning |
|--------|---------------------|
| Green | ADD & CMD Signals |
| Yellow | Clocks |
| Pink | Data Byte Group 0 |
| Purple | Data Byte Group 1 |
| Blue | Data Byte Group 2 |
| Brown | Data Byte Group 3 |
| Gray | DDR_1V35 & DDR_VREF |
| Red | Control Signals |

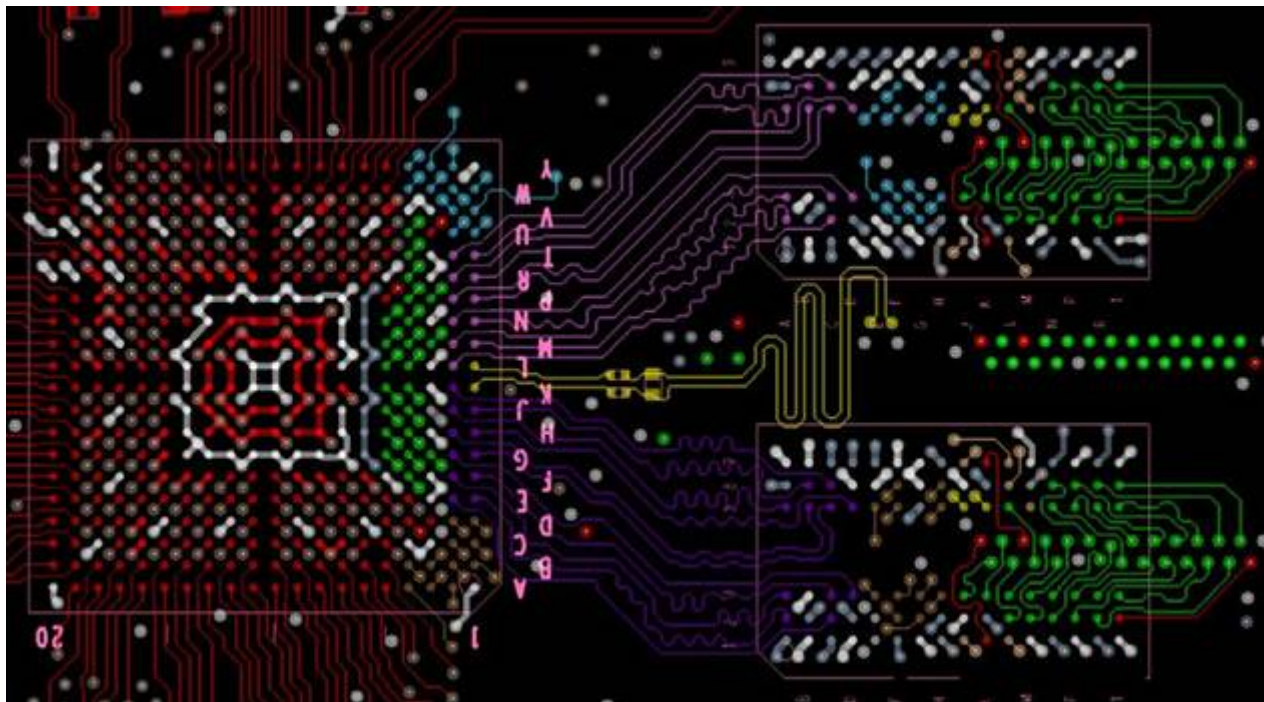


Figure 3-10. Top layer T-topology DDR3 routing

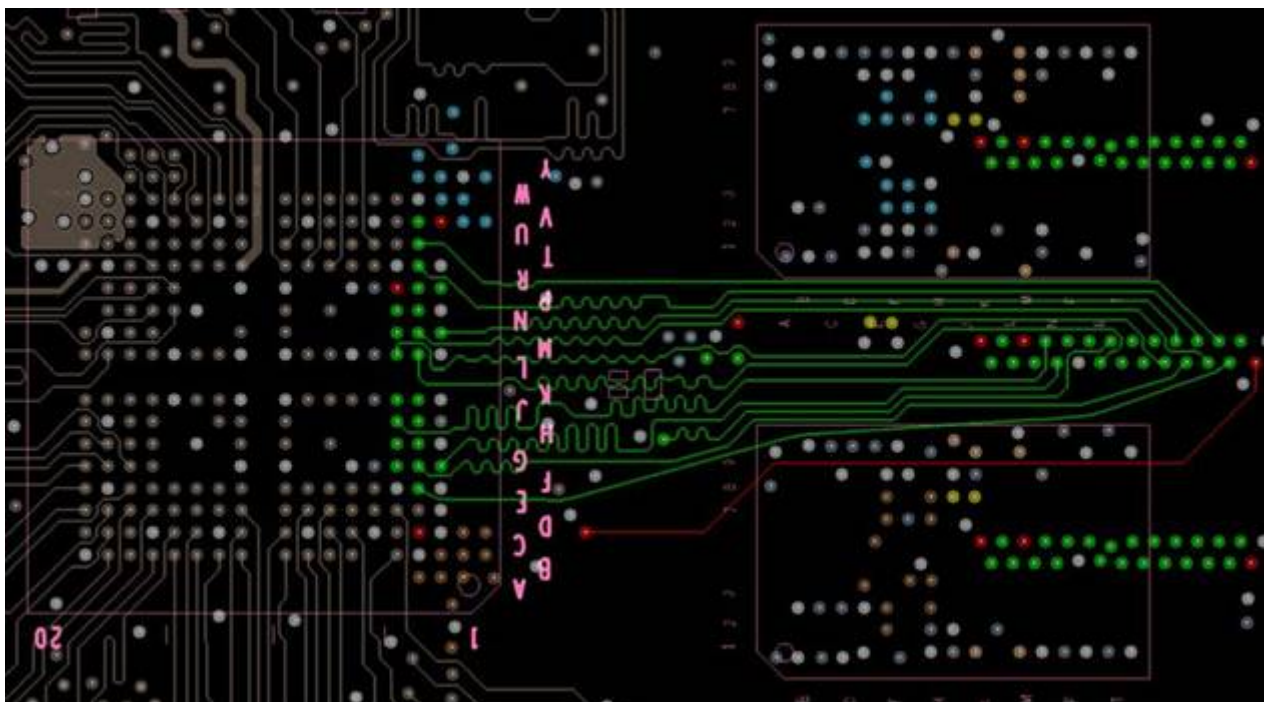


Figure 3-11. Internal L3 T-topology DDR3 routing

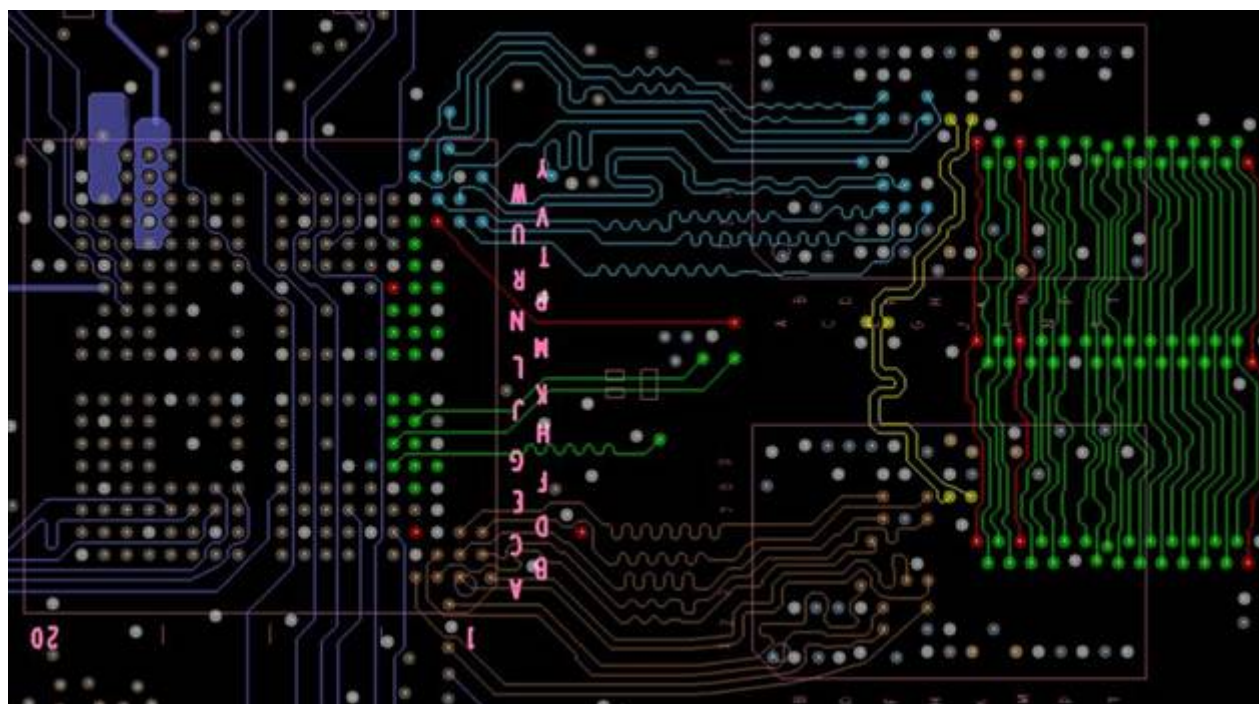


Figure 3-12. Internal L5 T-topology DDR3 routing

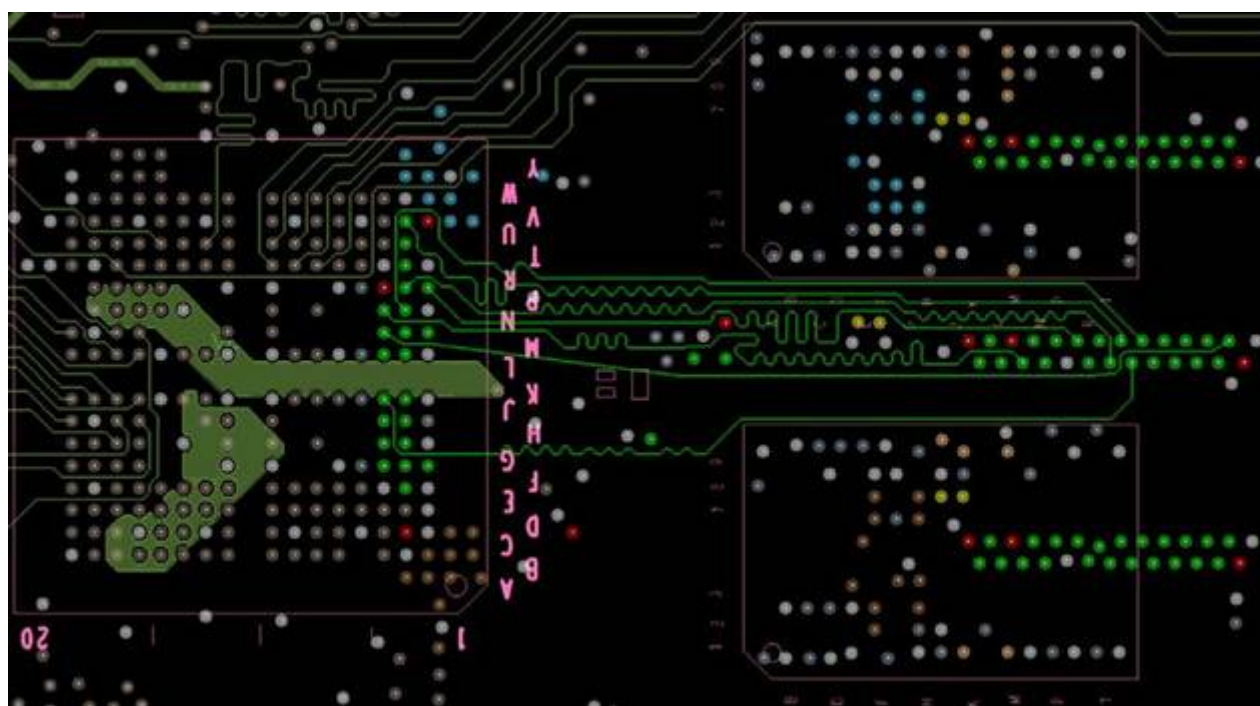


Figure 3-13. Internal L10 T-topology DDR3 routing

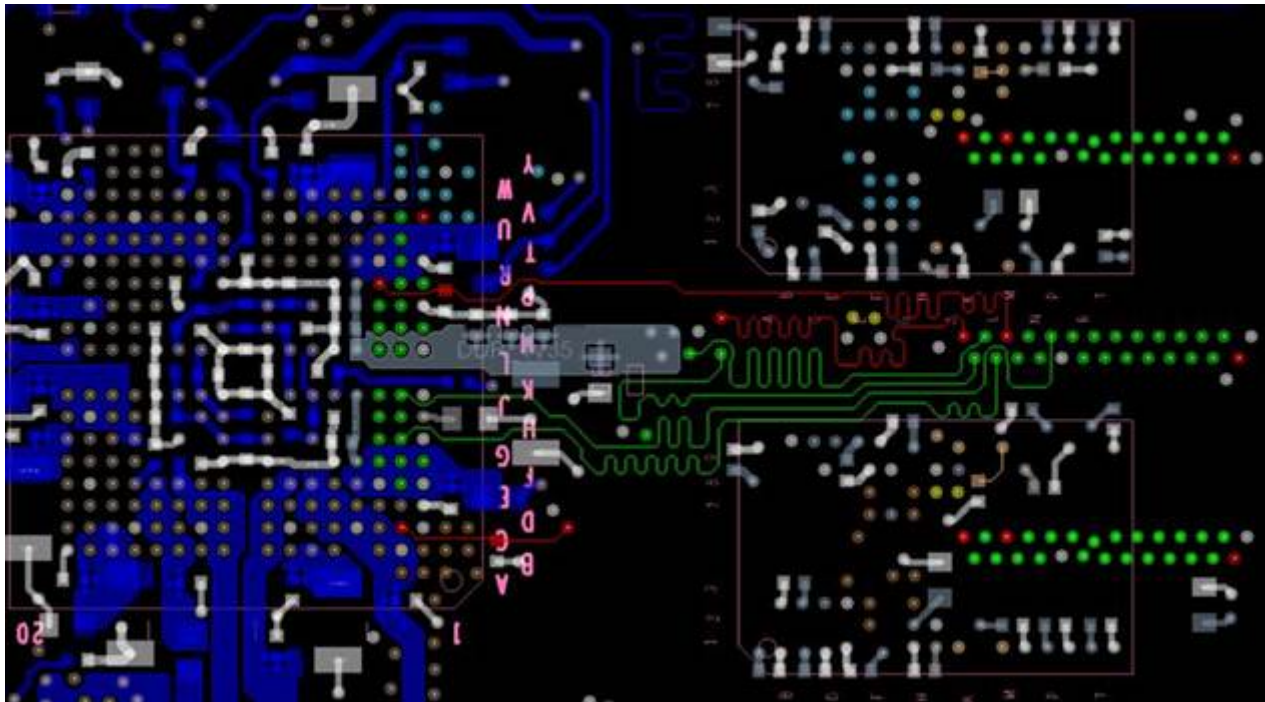


Figure 3-14. Bottom layer T-topology DDR3 routing

The following table shows the total etch of the signals for the byte 0 and byte 1 groups. The layout is an example, using 1790 mils for the clock.

Table 3-6. Total signal etch (DDR3)

| Signals | Length (Mils) |
|--------------|---------------|
| DRAM_D0 | 668.879 |
| DRAM_D1 | 669.081 |
| DRAM_D2 | 668.418 |
| DRAM_D3 | 669.224 |
| DRAM_D4 | 667.319 |
| DRAM_D5 | 669.851 |
| DRAM_D6 | 667.602 |
| DRAM_D7 | 668.021 |
| DRAM_DQM0 | 669.672 |
| DRAM_SDQS0 | 671.056 |
| DRAM_SDQS0_B | 671.493 |
| DRAM_D8 | 677.254 |
| DRAM_D9 | 675.478 |
| DRAM_D10 | 675.902 |
| DRAM_D11 | 677.141 |
| DRAM_D12 | 677.912 |
| DRAM_D13 | 679.458 |
| DRAM_D14 | 677.199 |

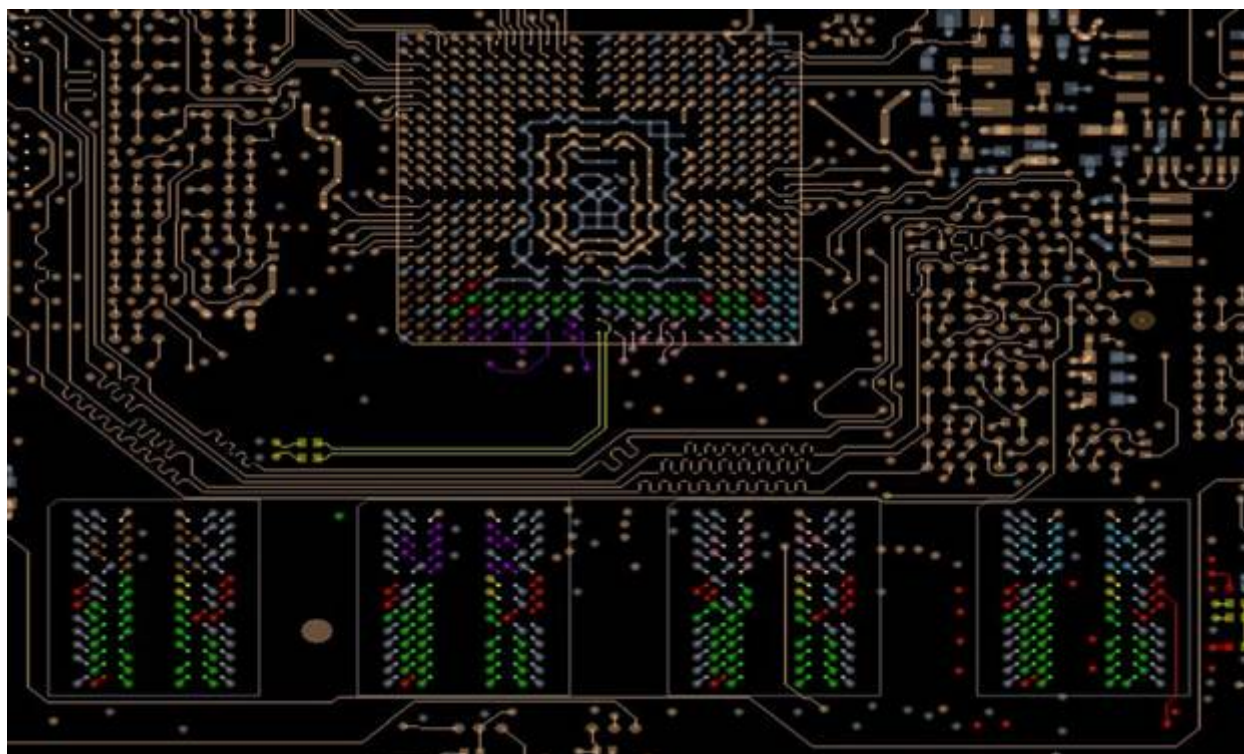
Table continues on the next page...

Table 3-6. Total signal etch (DDR3) (continued)

| | |
|---------------|----------|
| DRAM_D15 | 679.199 |
| DRAM_DQM1 | 678.342 |
| DRAM_SDQS1 | 680.463 |
| DRAM_SDQS1_B | 680.649 |
| DRAM_SDCLK0 | 1789.627 |
| DRAM_SDCLK0_B | 1789.648 |

3.5.7 Four chips fly-by topology routing examples

The figures in this section show examples for the routing of 2-Gbyte DDR memories. These figures are a guideline of the routing by layer using the fly by configuration topology. They use the same color code shown in [Table 3-5](#).

**Figure 3-15. Top fly-by DDR3 routing**

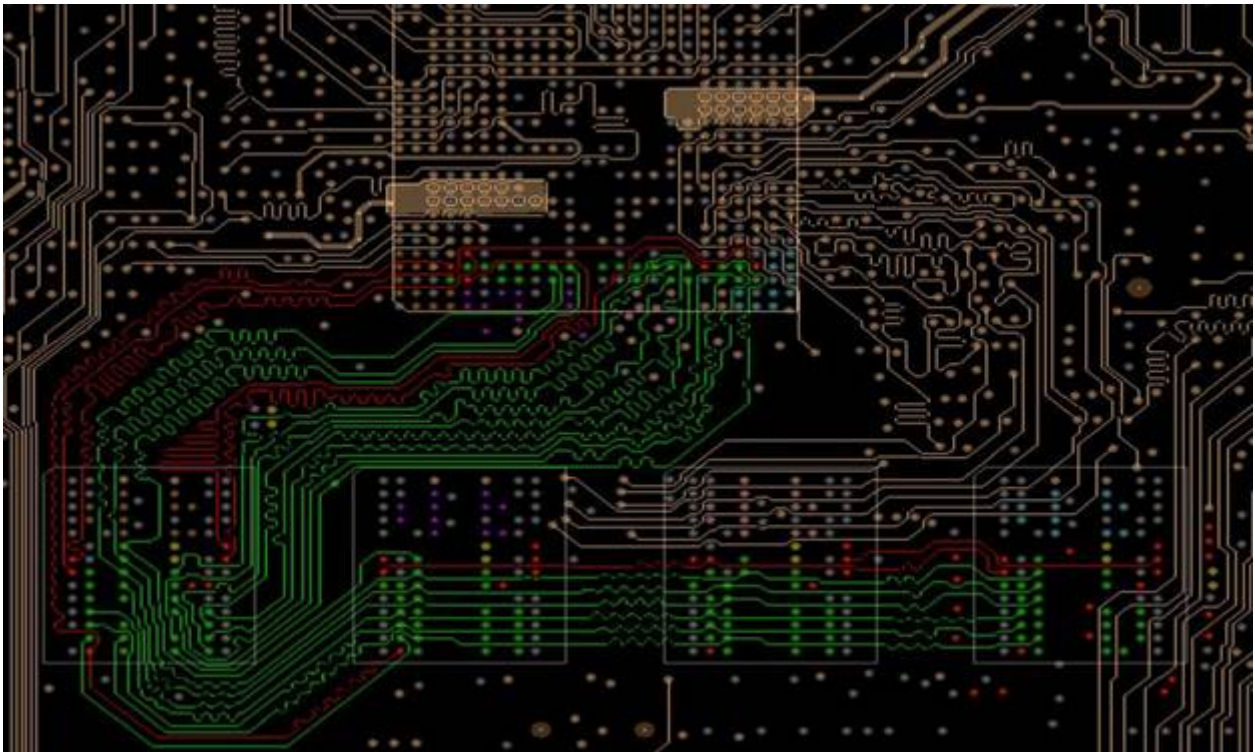


Figure 3-16. Internal L3 fly-by DDR3 routing

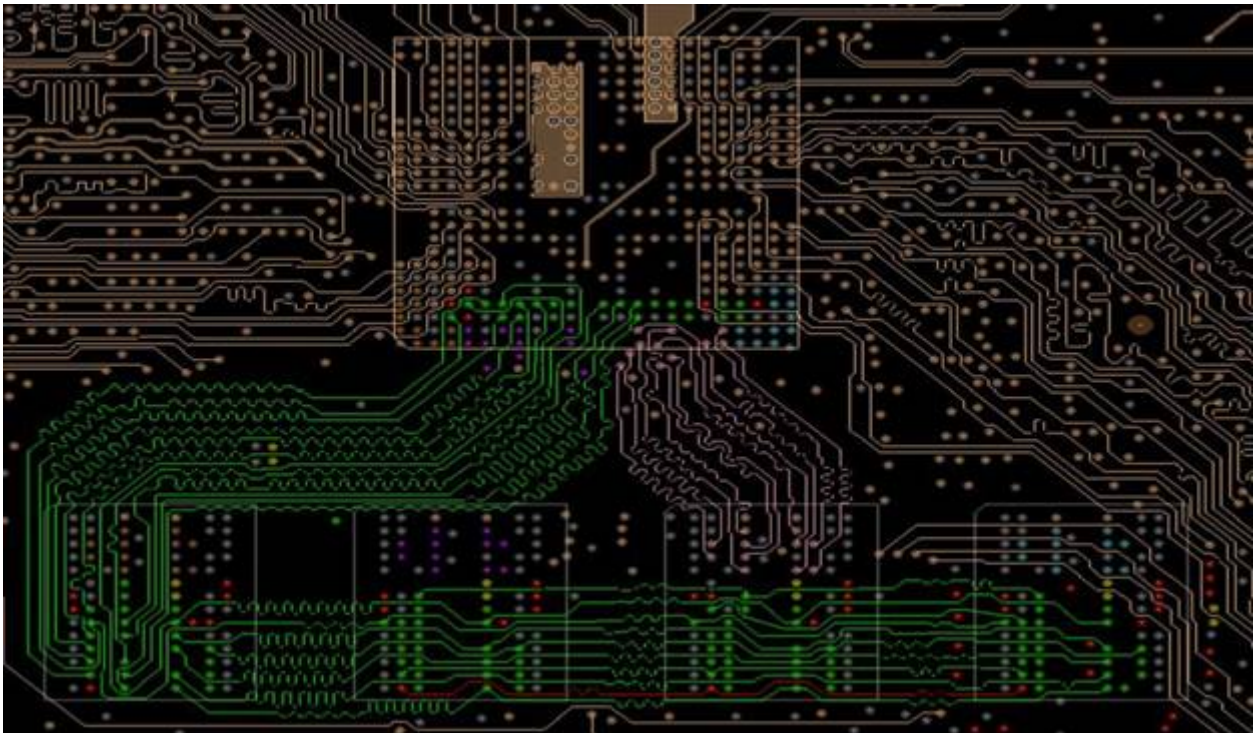


Figure 3-17. Internal L5 fly-by DDR3 routing

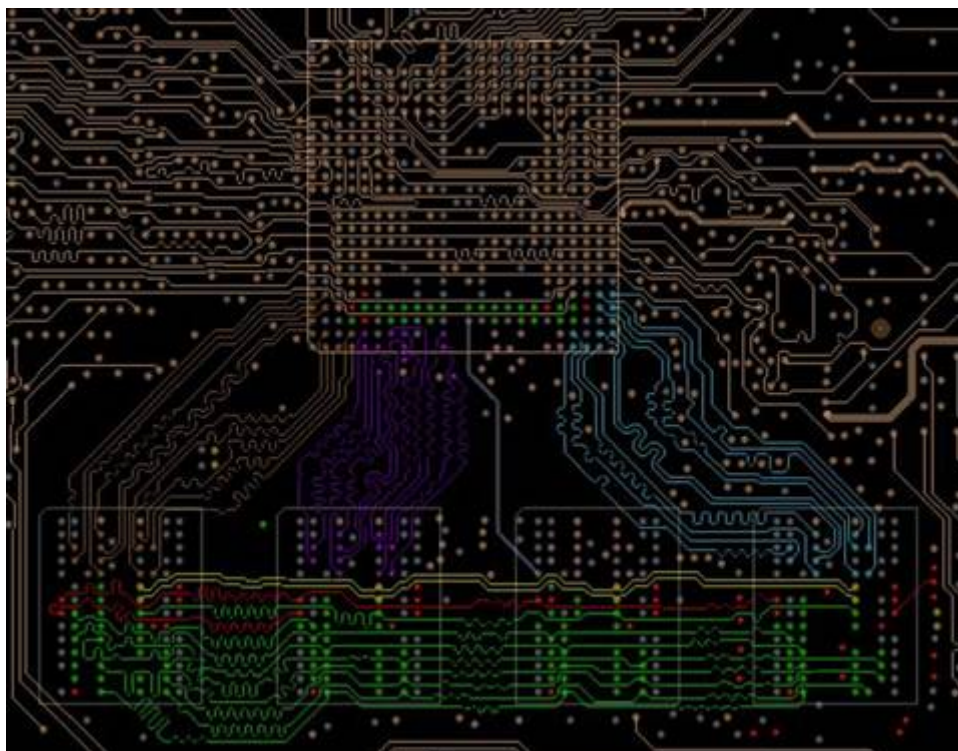


Figure 3-18. Internal L10 fly-by DDR3 routing

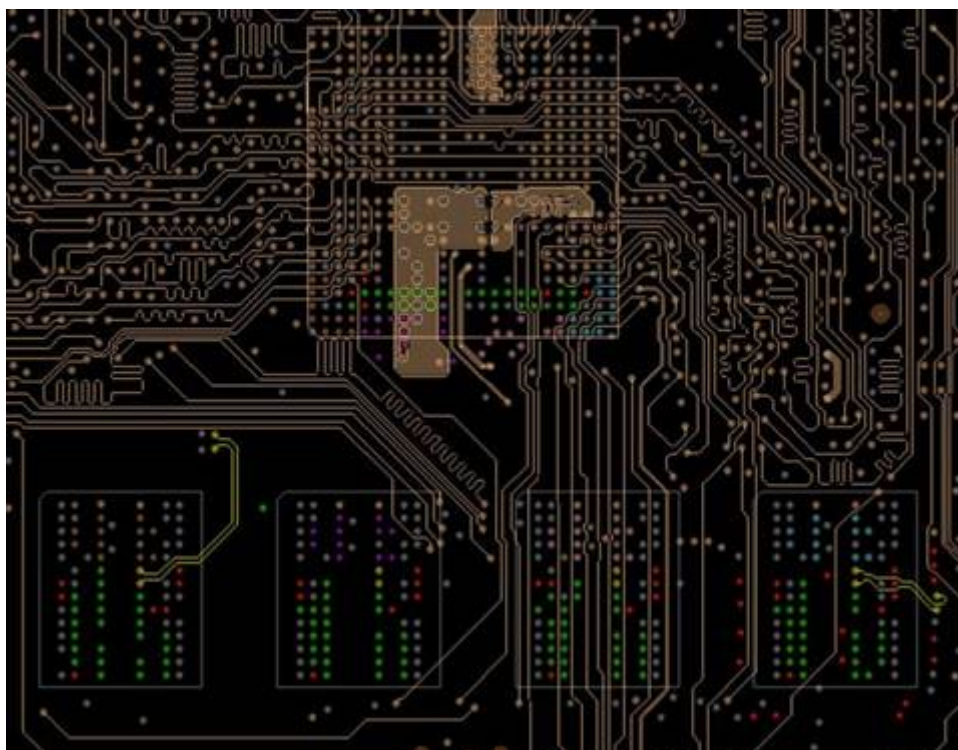


Figure 3-19. Internal L12 fly-by DDR3 routing

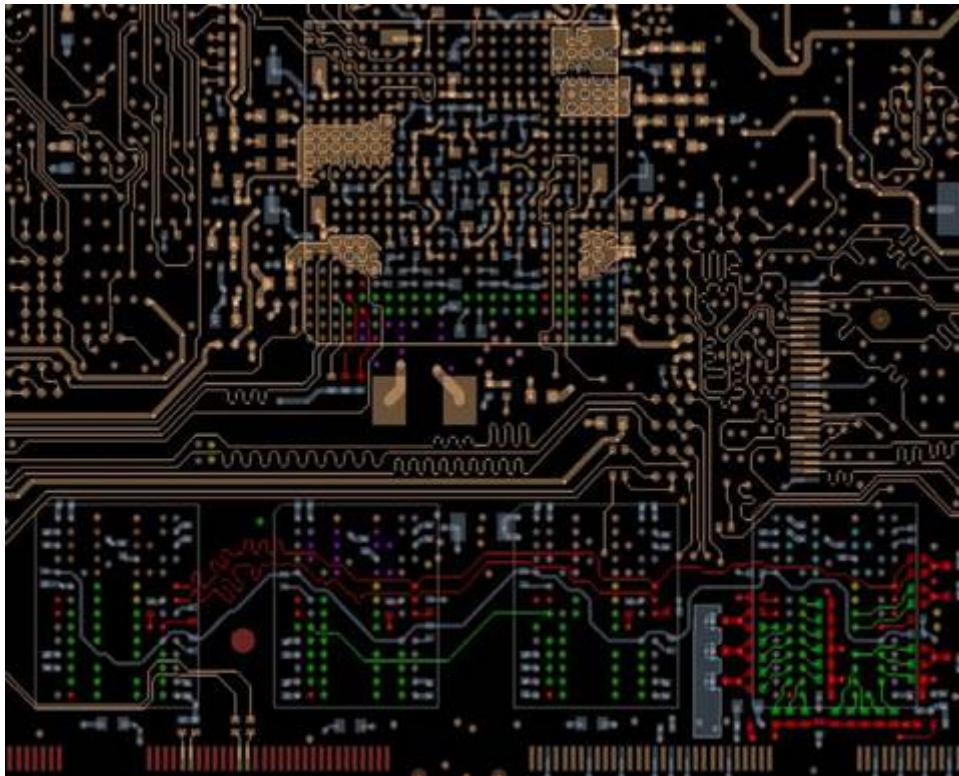


Figure 3-20. Internal Bottom fly-by DDR3 routing

Table 3-7. Total signal etch fly-by DDR3

| Signals | Length (Mils) |
|--------------|---------------|
| DRAM_D0 | 787.572 |
| DRAM_D1 | 790.338 |
| DRAM_D2 | 790.323 |
| DRAM_D3 | 790.007 |
| DRAM_D4 | 786.924 |
| DRAM_D5 | 790.014 |
| DRAM_D6 | 788.058 |
| DRAM_D7 | 790.905 |
| DRAM_DQM0 | 790.300 |
| DRAM_SDQS0 | 786.391 |
| DRAM_SDQS0_B | 785.699 |
| DRAM_D8 | 801.213 |
| DRAM_D9 | 802.533 |
| DRAM_D10 | 808.059 |
| DRAM_D11 | 803.854 |
| DRAM_D12 | 805.219 |
| DRAM_D13 | 801.782 |
| DRAM_D14 | 802.879 |

Table continues on the next page...

Table 3-7. Total signal etch fly-by DDR3 (continued)

| | |
|------------------------|----------|
| DRAM_D15 | 801.067 |
| DRAM_DQM1 | 804.210 |
| DRAM_SDQS1 | 804.016 |
| DRAM_SDQS1_B | 803.209 |
| DRAM_SDCLK0 (Byte0) | 2779.48 |
| DRAM_SDCLK0_B (Byte 0) | 2759.761 |
| DRAM_SDCLK0 (Byte1) | 2105.156 |
| DRAM_SDCLK0_B (Byte 1) | 2083.168 |

3.5.8 High speed signal routing recommendations

The following list provides recommendations for routing traces for high speed signals. Note that the propagation delay and the impedance control should match in order to have the correct communication with the devices.

- High-speed signals (DDR, RGMII, display) must not cross gaps in the reference plane.
- Avoid creating slots, voids, and splits in reference planes. Review via voids to ensure they do not create splits (space out vias).
- Provide ground return vias within 100 mils distance from signal layer-transition vias when transitioning between different reference ground planes.
- A solid GND plane must be directly under crystal, associated components, and traces.
- Clocks or strobes that are on the same layer need at least 2.5× spacing from an adjacent trace (2.5× height from reference plane) to reduce cross-talk.
- All synchronous modules should have bus length matching and relative clock length control. For SD module interfaces:
 - Match data and CMD trace lengths (length delta depends on bus rates)
 - CLK should be longer than the longest signal in the Data/CMD group (+5 mils)
 - Similar DDR rules must be followed for data, address and control as for SD module interfaces.

3.5.9 Ground plane recommendations

This section provides examples of good practices and how to avoid common user mistakes when flowing the ground planes layers.

The following two figures show common examples of poor GND planes.

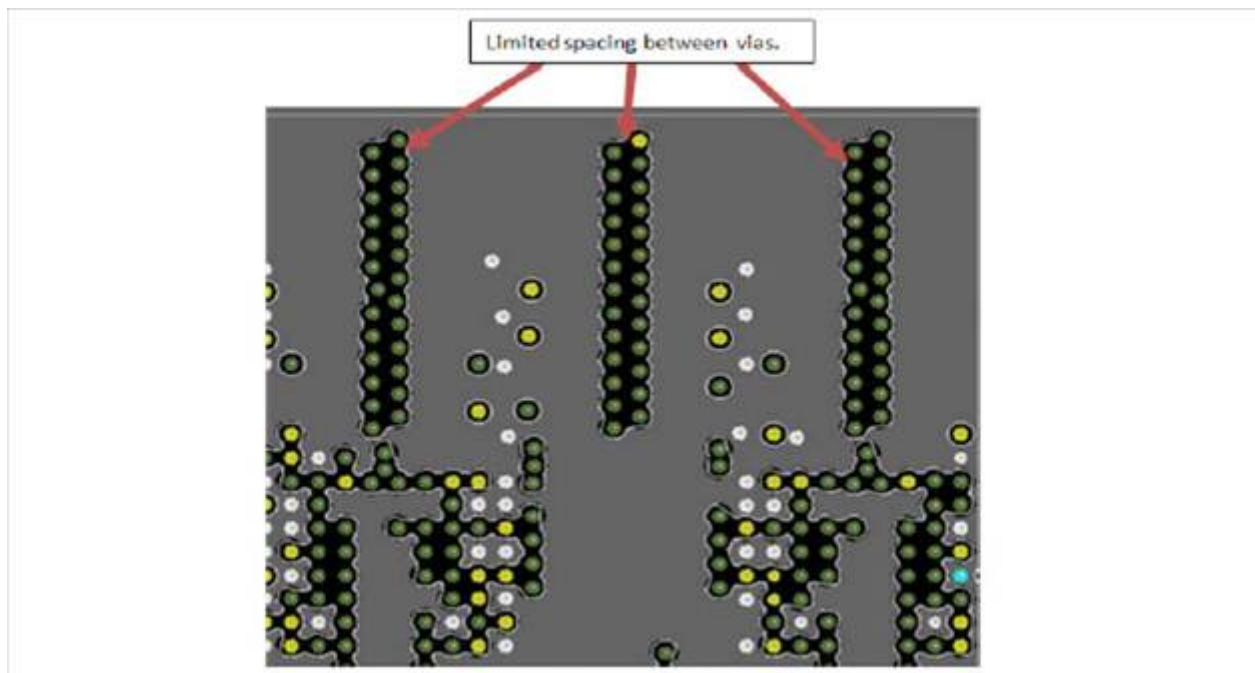


Figure 3-21. Poor GND plane 1

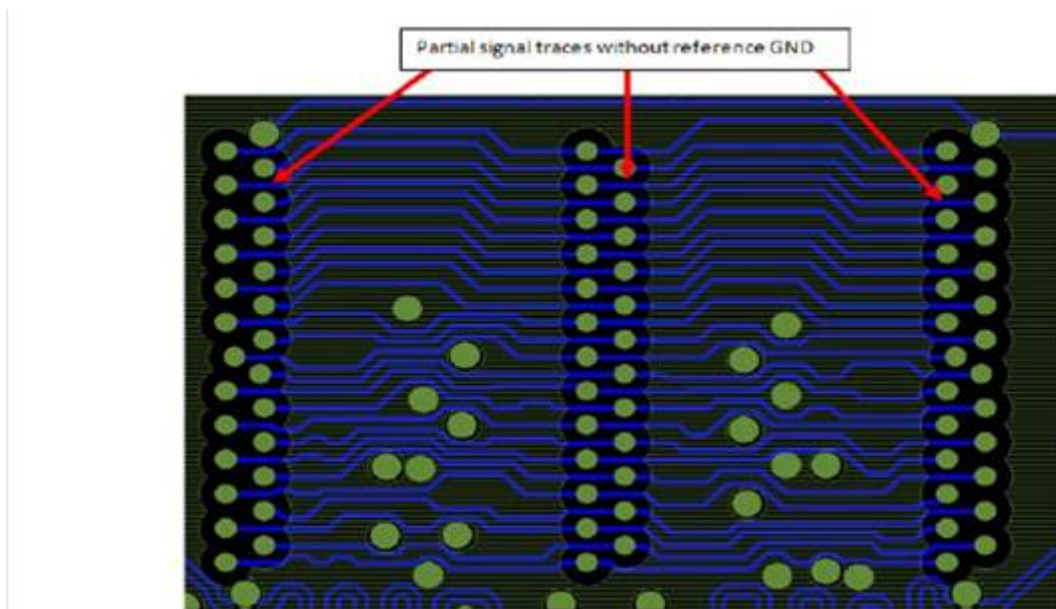


Figure 3-22. Poor GND plane 2

Spacing the vias some mils apart facilitates the GND copper flowing in the plane. The following figures show good practices of ground planes.

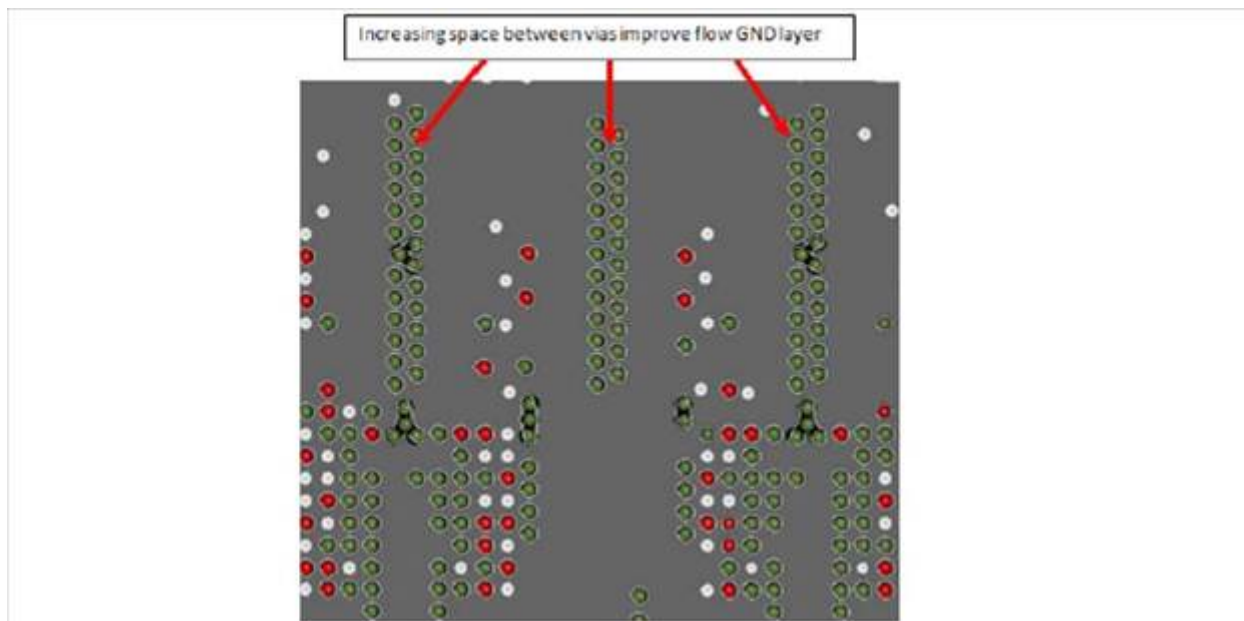


Figure 3-23. Good layout GND plane detail

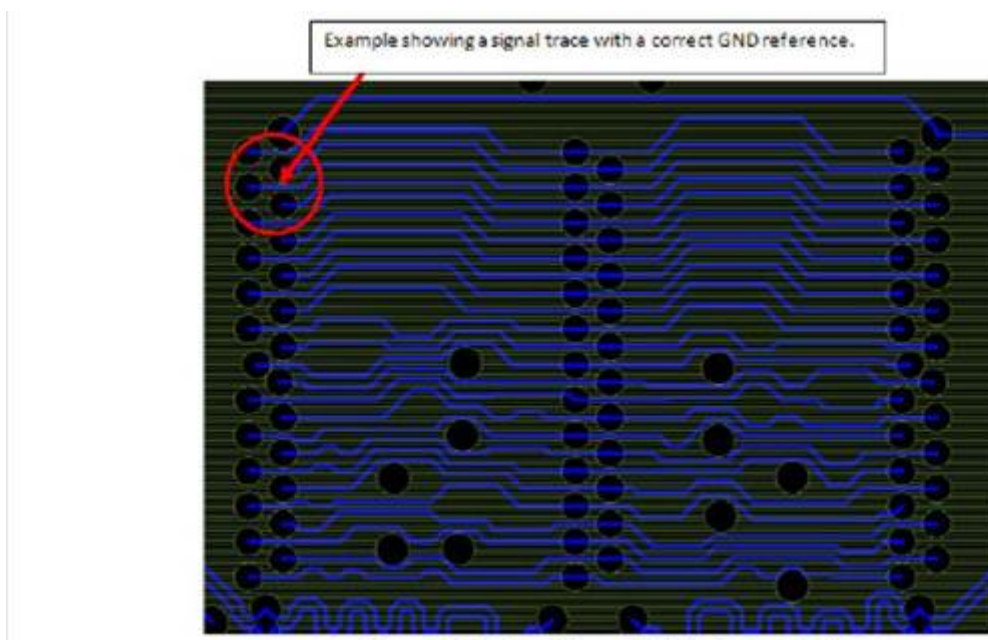


Figure 3-24. Good layout GND plane detail

3.6 DDR power recommendations

The following recommendations apply to the VREF (P0V675_REFDDR) voltage reference plane.

- Use 30 mils trace between decoupling cap and destination.

- Maintain a 25 mils clearance from other nets.
- Isolate VREF and/or shield with ground.

Decouple using distributed 0.22 μ F capacitors by the regulator, controller, and devices.

- Place one 1.0 μ F near the source of VREF: one near the VREF pin on the controller and two between the controller and the devices.

The following recommendations apply to the VTT (DDR_VTT) voltage reference plane. The figures are examples from the evaluation board for the VTT reference schematic.

- Place the VTT island on the component side layer at the end of the bus behind the DRAM devices.
- Use a wide-island trace for current capacity.
- Place the VTT generator as close to termination resistors as possible to minimize impedance (inductance).
- Place one or two 0.1 μ F decoupling capacitors by each termination RPACK on the VTT island to minimize the noise on VTT. Other bulk (10–22 pF) decoupling is also recommended to be placed on the VTT island.

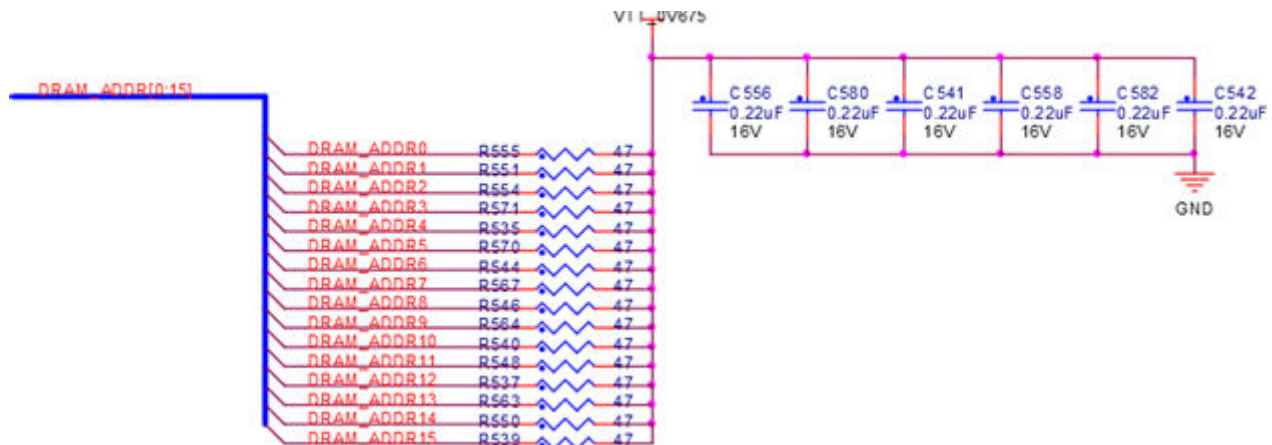


Figure 3-25. DDR_VTT validation board example

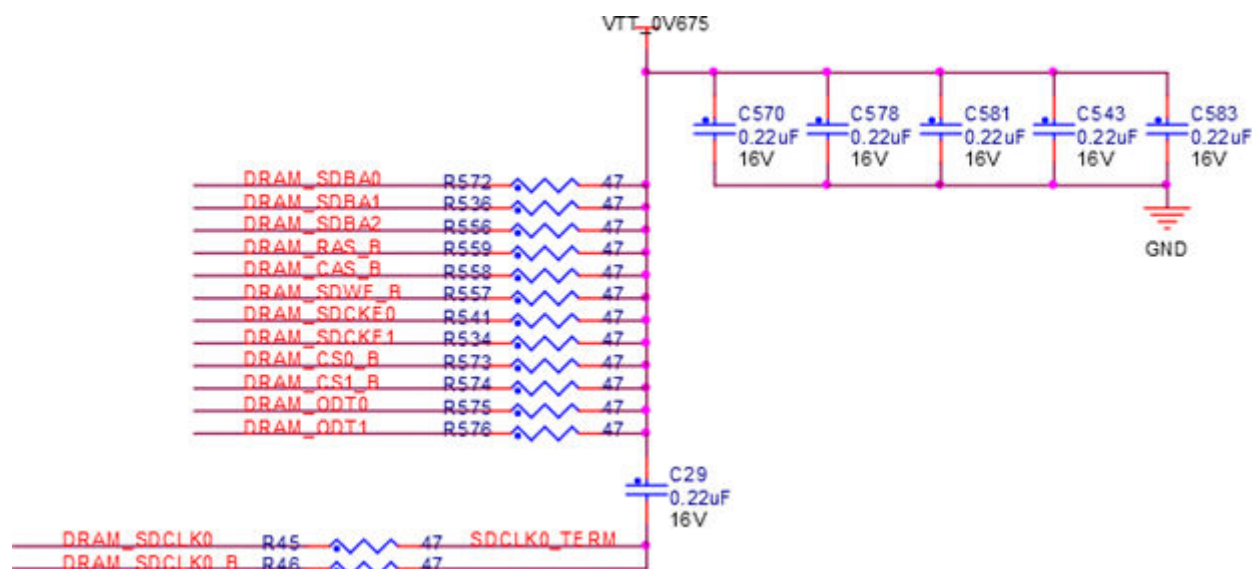


Figure 3-26. DDR_VTT validation board examples

3.7 PCI Express interface recommendations

This chip provides a $\times 1$ PCIe lane. The PCIe module supports PCI Express Gen 2.0 interfaces at 5 Gb/s. It is also backwards compatible to Gen 1.1 interfaces at 2.5 Gb/s.

NOTE

Lane $\times 1$ is composed of two differential signals pairs: one TXD signal pair and one RXD signal pair.

Table 3-8. PCI Express signal descriptions

| Signal name | Signal group | Description |
|----------------------|--------------|--|
| PCIE_TX_P, PCIE_TX_N | Data | PCI Express transmit differential pair |
| PCIE_RX_P, PCIE_RX_N | Data | PCI Express receive differential pair |

3.7.1 PCI Express general routing guidelines

Use the following recommendations for PCI Express general routing:

- The trace width and spacing of the lanes $\times 1$ signals should be such that the differential impedance is $85\ \Omega \pm 10\%$.
- The PCIE_REXT contacts should be connected to a $200\ \Omega$ 1% resistor to ground. The trace length between the pin and the resistor should be minimized. The resistor value is defined within the data sheet and should determine the exact resistor value.

- Route traces over continuous planes (power and ground).
 - They should not pass over any power/GND plane slots or anti-etch.
 - When placing connectors, make sure the ground plane clear-outs around each pin have ground continuity between all pins.
- Maintain the parallelism (skew matched) between DP and DM, and match overall differential length difference to less than 5 mils.
- Maintain symmetric routing for each differential pair.
- Do not route DP and DM traces under oscillators or parallel to clock traces and/or data buses.
- Minimize the lengths of high speed signals that run parallel to the DP and DM pair.
- Keep DP and DM traces as short as possible.
- Route DP and DM signals with a minimum amount of corners. Use 45-degree turns instead of 90-degree turns.
- Avoid layer changes (vias) on DP and DM signals. Do not create stubs or branches.
- Provide ground return vias within 50 mils distance from signal layer-transition vias when transitioning between different reference ground planes.

3.7.1.1 PCI Express coupling lane

Based on our development design, we have the following coupling signal schema. Consult the PCISig documentation for detailed information.

- DC-coupled Rx signals with 0 Ω resistors
- AC-coupled Tx signals with 0.1 μ F capacitors

3.7.1.2 Additional resources for PCI Express signal routing recommendations

For more information about, PCI Express signal routing recommendations, see the following.

- NXP Hardware Design Considerations for PCI Express® and SGMII (http://www.nxp.com/files/training_presentation/TP_HARDWARE_DESIGN_PCI_SMGIII.pdf)
- PCISig, PCI Express Base Specification.
- PCISig, PCI Express Card Electromechanical Specification.
- PCISig, PCSIG Board Design Guidelines for PCI Express™ Architecture.
- PCI Express Basics: Developing Physical Design Rules for PCIe (<http://www.mentor.com/products/pcb-system-design/multimedia/pcie-basics-webinar>)

3.7.2 LVDS recommendations

Use the following recommendations for the LVDS.

- Follow standard high-speed differential routing rules for signal integrity.
- Each differential pair should be length matched to ± 5 mils.
- LVDS differential pairs should have a differential impedance of 100 Ω .

3.7.3 USB recommendations

Use the following recommendations for the USB.

- Route the high speed clocks and the DP and DM differential pair first.
- Route DP and DM signals on the top or bottom layer of the board
- The trace width and spacing of the DP and DM signals should meet the differential impedance requirement of 90 Ω .
- Route traces over continuous planes (power and ground).
 - They should not pass over any power/GND plane slots or anti-etch.
 - When placing connectors, make sure the ground plane clearouts around each pin have ground continuity between all pins.
- Maintain the parallelism (skew matched) between DP and DM, and match overall differential length difference to less than 5 mils.
- Maintain symmetric routing for each differential pair.
- Do not route DP and DM traces under oscillators or parallel to clock traces and/or data buses.
- Minimize the lengths of high speed signals that run parallel to the DP and DM pair.
- Keep DP and DM traces as short as possible.
- Route DP and DM signals with a minimum amount of corners. Use 45-degree turns instead of 90-degree turns.
- Avoid layer changes (vias) on DP and DM signals. Do not create stubs or branches.
- Provide ground return vias within 50 mils distance from signal layer-transition vias when transitioning between different reference ground planes.

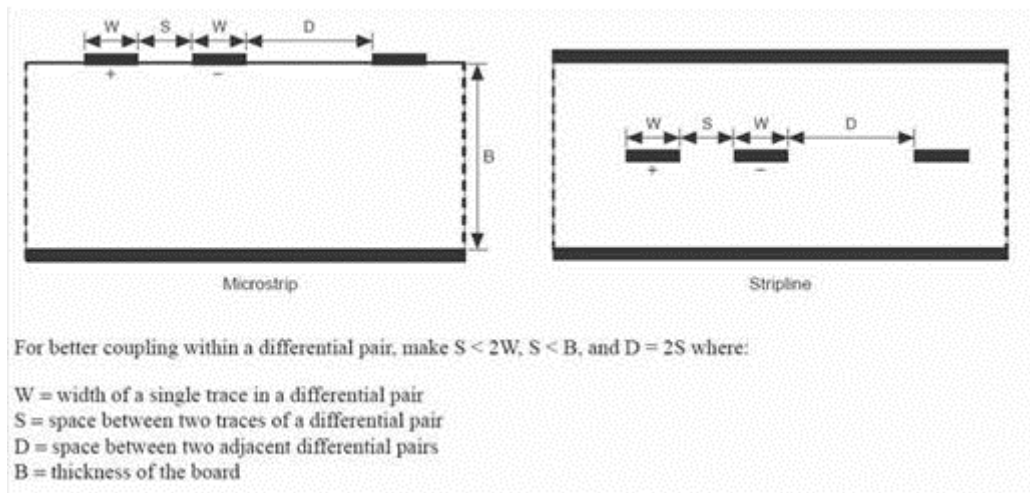
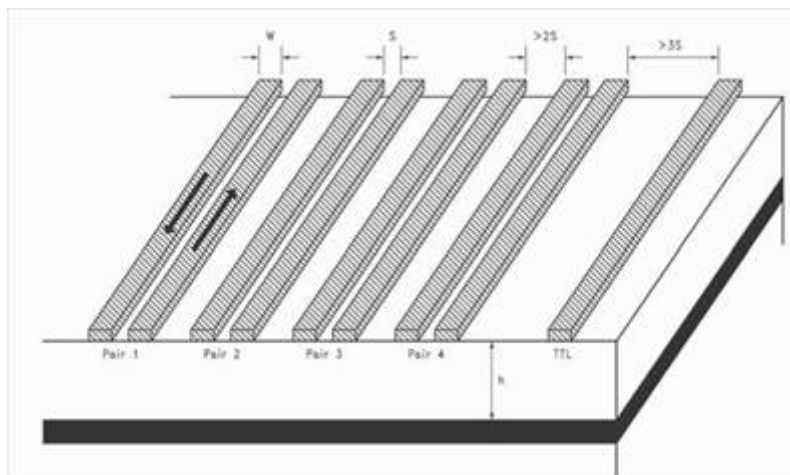
3.7.4 Impedance signal recommendations

Use the following table as a reference when you are updating or creating constraints in your software PCB tool to set up the impedance and the correct trace width.

Table 3-9. Impedance signal recommendations

| Signal Group | Impedance | Layout Tolerance (\pm) |
|---|-------------------|----------------------------|
| All signals, unless specified | 50 Ω SE | 10% |
| PCIe Diff signals | 85 Ω Diff | 10% |
| USB Diff signals | 90 Ω Diff | 10% |
| Diff signals: LVDS, DDR, Phy IC to Ethernet Connector | 100 Ω Diff | 10% |

The following figure shows the dimensions of a stripline and microstrip pair. [Figure 3-28](#) shows the differential pair routing.

**Figure 3-27. Microstrip and stripline differential pair dimensions****Figure 3-28. Differential pair routing**

- The space between two adjacent differential pairs should be greater than or equal to twice the space between the two individual conductors.
- The skew between LVDS pairs should be within the minimum recommendation (± 100 mil).

3.7.5 Reference resistors

NOTE

The reference resistor and the connection should be placed away from noisy regions. Noise induced on it may impact the internal circuit and degrade the interface signals.

3.7.6 ESD and radiated emissions recommendations

The PCB design should use six or more layers, with solid power and ground planes. The recommendations for ESD immunity and radiated emissions performance are as follows:

- All components with ground chassis shields (USB jack, buttons, and so forth) should connect the shield to the PCB chassis ground ring.
- Ferrite beads should be placed on each signal line connecting to an external cable. These ferrite beads must be placed as close to the PCB jack as possible.

NOTE

Ferrite beads should have a minimum impedance of $500\ \Omega$ at 100 MHz with the exception of the ferrite on USB_5V.

- Ferrite beads should NOT be placed on the USB D+/D– signal lines as this can cause USB signal integrity problems. For radiated emissions problems due to USB, a common mode choke may be placed on the D+/D– signal lines. However, in most cases, it should not be required if the PCB layout is satisfactory. Ideally, the common mode choke should be approved for high speed USB use or tested thoroughly to verify there are no signal integrity issues created.
- It is highly recommended that ESD protection devices be used on ports connecting to external connectors. See the reference schematic (available at www.nxp.com) for detailed information about ESD protection implementation on the USB interfaces.
- If possible, stitch all around the board with vias with 100 mils spacing between them connected to GND planes with exposed solder mask to improve EMI.

3.7.7 Component placement recommendations

Adhere to the following recommendations when placing components.

- Place components such that short and/or critical routes can be easily laid out.
 - Critical routes determine component location.
 - Orient devices to facilitate routes (minimize length and crossovers).
- Consider placing the following pairings adjacent.
 - i.MX and DDR
 - PHY and associated jack
 - Jack and CODEC input
 - Bluetooth® (or other RF) and antenna

3.7.8 Reducing skew and phase problems in differential pairs traces

Differential pair technology has evolved to require more stringent checking in the area of phase control. This is evident on the higher data rates associated with parallel buses such as PCI Gen 2, DDR, LVDS, or Ethernet. In the simplest of terms, Diff Pair technology sends opposite and equal signals down a pair of traces. Keeping these opposite signals in phase is essential to assuring that they function as intended.

[Figure 3-29](#) and [Figure 3-30](#) show two examples of static routing where a match is achieved without needing to tune one element of the differential pair.

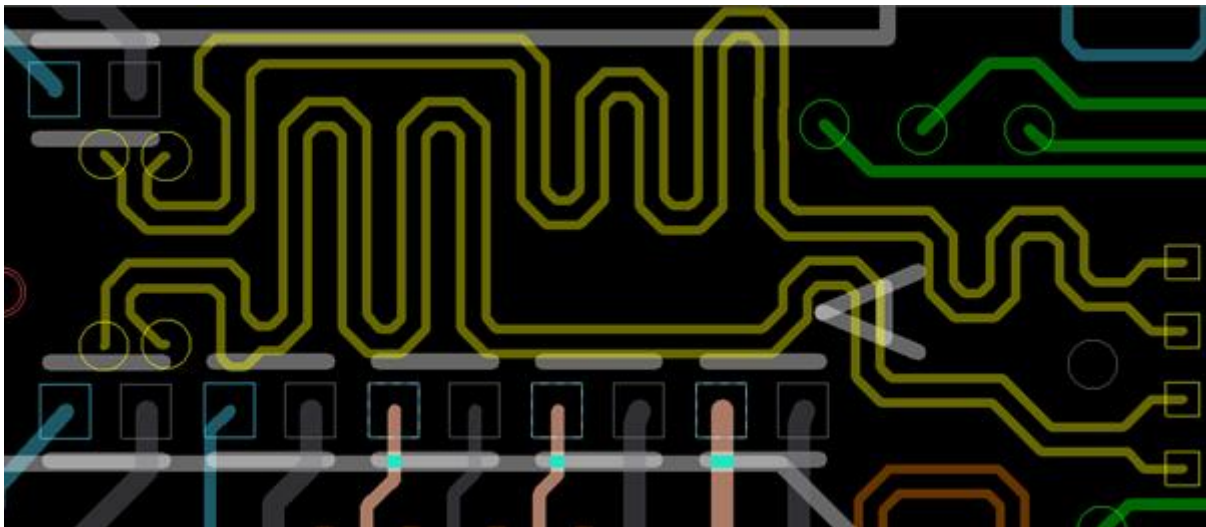


Figure 3-29. Yellow traces diff pairs 1

The following figure shows the addition of a delay trace to one element of the differential pair to avoid length mismatch (which reduces skew and phase problems). The green box marks the detail.

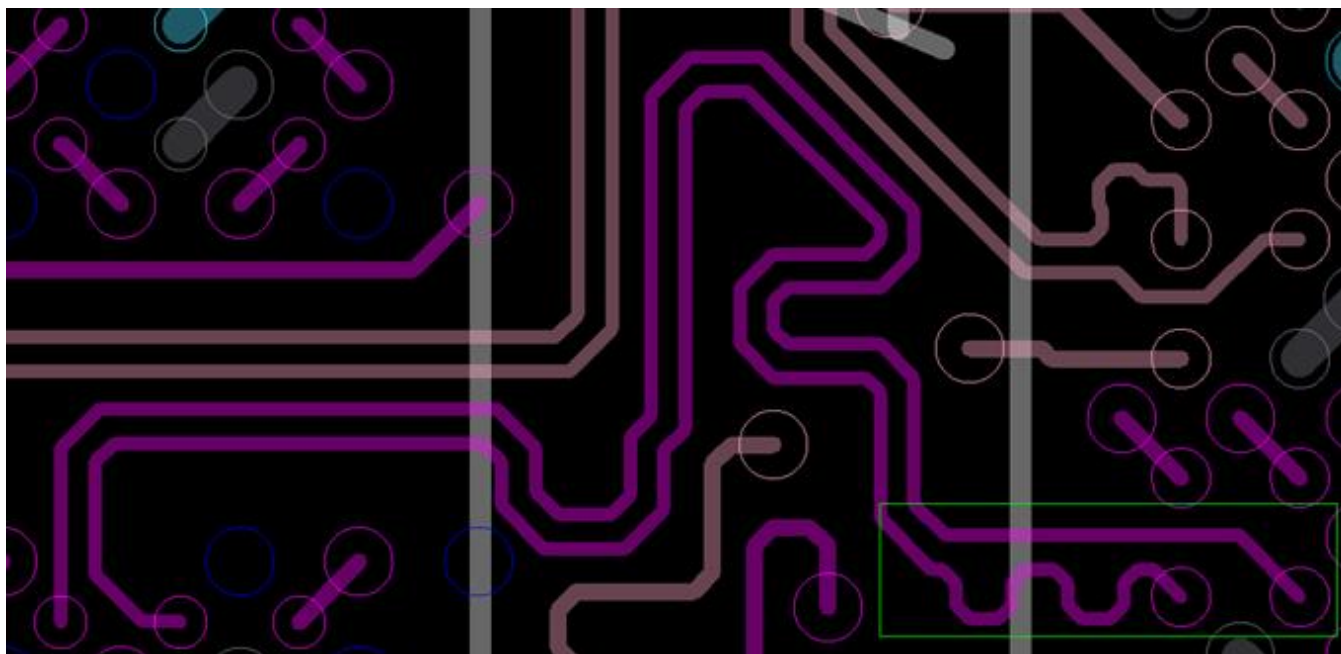


Figure 3-30. Small bumps added to the shorter differential pair

Chapter 4

Avoiding Board Bring-up Problems

4.1 Introduction

This chapter provides recommendations for avoiding typical mistakes when bringing up a board for the first time. These recommendations consist of basic techniques that have proven useful in the past for detecting board issues and addressing the three most typical bring-up pitfalls: power, clocks, and reset. A sample bring-up checklist is provided at the end of the chapter.

4.2 Using a current monitor to avoid power pitfalls

Excessive current can cause damage to the board. Avoid this problem by using a current-limiting laboratory supply set to the expected typical main current draw (at most). Monitor the main supply current with an ammeter when powering up the board for the first time. You can use the supply's internal ammeter if it has one. By monitoring the main supply current and controlling the current limit, any excessive current can usually be detected before permanent damage occurs.

4.3 Using a voltage report to avoid power pitfalls

Using incorrect voltage rails is a common power pitfall. To help avoid this mistake, create a basic table called a voltage report prior to bringing up your board. This table helps validate that all the supplies are reaching the expected levels.

To create a voltage report, list the following:

- Your board voltage sources
- Default power-up values for the board voltage sources
- Best location on the board to measure the voltage level of each supply

Carefully determine the best measurement location for each power supply to avoid a large voltage drop (IR drop) on the board, which causes inaccurate current values to be measured. The following guidelines help produce the best current measurements:

- Measure closest to the load (in this case the i.MX6 processor).
- Make two measurements: the first after initial board power-up and the second while running a heavy use-case that stresses the i.MX6 processor.

Ensure that the supplies that are powering the i.MX6 meet the DC electrical specifications as listed in your chip-specific data sheet.

The shaded cells in the PMIC LDO2 row call your attention to the difference in the expected value and measured value, which indicates a potential problem with that power rail.

Table 4-1. Sample voltage report

| Source | Net name | Expected (V) | Measured (V) | Measured point | Comment |
|--------------------|-------------|--------------|--------------|----------------|-------------------------|
| Main | 5V0 | 5.0 | 5.103 | C5.1 | — |
| 3.3 V discrete reg | 3V3_DELAYED | 3.35 | 3.334 | SH1 | Requires LDO3 to enable |
| PMIC Switcher 1 | VDDARM | 1.375 | 1.377 | SH2 | — |
| PMIC Switcher 2 | VDDSOC | 1.375 | 1.376 | SH3 | — |
| PMIC Switcher 3 | 1V5_DDR | 1.5 | 1.501 | SH4 | — |
| PMIC LDO1 | 1V8 | 1.8 | 1.802 | TP9 | — |
| PMIC LDO2 | 2V5 | 2.5 | 0.3 | TP5 | — |
| VREFDDR | 0V75_REFDDR | 0.75 | 0.751 | C8.1 | 50% of 1V5_DDR |
| Coin Cell | 3V0_STBY | 3.0 | 3.006 | TP1 | — |
| i.MX6 | VDDARM_CAP | 1.1 | 1.114 | C6.1 | — |
| i.MX6 | VDDHIGH_CAP | 2.5 | 2.515 | SH5 | — |
| i.MX6 | VDDSNVS_CAP | 1.0 | 1.016 | TP2 | — |

4.4 Checking for clock pitfalls

Problems with the external clocks are another common source of board bring-up issues. Ensure that all of your clock sources are running as expected.

The XTALI/XTALO and the RTC_XTALI/RTC_XTALO clocks are the main clock sources for 24 MHz and 32 kHz reference clocks respectively on the i.MX6. Although not required, the use of low jitter external oscillators to feed CLK1_P/N or CLK2 on the i.MX6 can be an advantage if low jitter or special frequency clock sources are required

by modules driven by CLK1_P/N or CLK2. See the CCM chapter in your i.MX6 chip reference manual for details. If a 32.768 kHz crystal is not connected to the i.MX6, an on-chip ring oscillator is automatically used for the low-frequency clock source.

When checking crystal frequencies, use an active probe to avoid excessive loading. A parasitic probe typically inhibits the 32.768 kHz and 24 MHz oscillators from starting up. Use the following guidelines:

- RTC_XTALI clock is running at 32.768 kHz (can be generated internally or applied externally).
- XTALI/XTALO is running at 24 MHz (used for the PLL reference).
- CLK1_P/N/CLK2 can be used as oscillator inputs for low jitter special frequency sources.
- CLK1_P/N and CLK2 are optional.

In addition to probing the external input clocks, you can check internal clocks by outputting them at the debug signals CLKO1 and CLKO2 (iomuxed signals). See the CCM chapter in the chip reference manual for more details about which clock sources can be output to those debug signals.

4.5 Avoiding reset pitfalls

Follow these guidelines to ensure that you are booting using the correct boot mode.

- During initial power on while asserting the POR_B reset signal, ensure that 24 MHz clock is active before releasing POR_B.
- Follow the recommended power-up sequence specified in the i.MX6 data sheet.
- Ensure the POR_B signal remains asserted (low) until all voltage rails associated with bootup are on.

The GPIOs and internal fuses control how the i.MX6 boots. For a more detailed description about the different boot modes, see the system boot chapter of the chip reference manual.

4.6 Sample board bring-up checklist

Note that the checklist incorporates the recommendations described in the previous sections. Blank cells should be filled in during bring-up as appropriate.

Table 4-2. Board bring-up checklist

| Checklist Item | Details | Owner | Findings & status |
|--|--|-------|-------------------|
| Note: The following items must be completed serially. | | | |
| 1. Perform a visual inspection. | Check major components to make sure nothing has been misplaced or rotated before applying power. | | |
| 2. Verify all i.MX6 voltage rails. | <p>Confirm that the voltages match the data sheet's requirements. Be sure to check voltages not only at the voltage source, but also as close to the i.MX6 as possible (like on a bypass capacitor). This reveals any IR drops on the board that will cause issues later.</p> <p>Ideally all of the i.MX6 voltage rails should be checked, but VDD_ARM_IN and VDD_SOC_IN are particularly important voltages. These are the core logic voltages and must fall within the parameters provided in the i.MX6 data sheet.</p> <p>VDD_SNVS_IN, NVCC_JTAG, and NVCC_DRAM are also critical to the i.MX6 boot up.</p> <p>Note: NVCC_LVDS2V5 must be powered when using the chip DDR interface. This power input is used as the Pre-Driver power source for the DDR I/O pads.</p> | | |
| 3. Verify power-up sequence. | Verify that power on reset (POR_B) is de-asserted (high) after all power rails have come up and are stable. See the i.MX6 data sheet for details about power-up sequencing. | | |
| 4. Measure/probe input clocks (32 kHz, 24MHz, others). | Without a properly running clock, the i.MX6 will not function properly. | | |
| 5. Check JTAG connectivity | This is one of the most fundamental and basic access points to the i.MX6 to allow the debug and execution of low level code. | | |
| Note: The following items may be worked on in parallel with other bring up tasks. | | | |
| Access internal RAM. | Verify basic operation of the i.MX6 in system. Perform a basic test by performing a write-read-verify to the internal RAM. No software initialization is necessary to access internal RAM. | | |
| Verify CLK0 outputs (measure and verify default clock frequencies for desired clock output options) if the board design supports probing of the CLK0 pin. | <p>This ensures that the corresponding clock is working and that the PLLs are working.</p> <p>Note that this step requires chip initialization, for example via the JTAG debugger, to properly set up the IOMUX to output CLK0 and to set up the clock control module to output the desired clock. See the reference manual for more details.</p> | | |
| <p>Measure boot mode frequencies. Set the boot mode switch for each boot mode and measure the following (depending on system availability):</p> <ul style="list-style-type: none"> • NAND (probe CE to verify boot, measure RE frequency) • SPI-NOR (probe slave select and measure clock frequency) • MMC/SD (measure clock frequency) | <p>This verifies the specified signals' connectivity between the i.MX6 and boot device and that the boot mode signals are properly set.</p> <p>See the "System Boot" chapter in the reference manual for details about configuring the various boot modes.</p> | | |

Table continues on the next page...

Table 4-2. Board bring-up checklist (continued)

| | | | |
|---|---|--|--|
| Run basic DDR initialization and test memory. | <ol style="list-style-type: none"> 1. Assuming the use of a JTAG debugger, run the DDR initialization and open a debugger memory window pointing to the DDR memory map starting address. 2. Try writing a few words and verify if they can be read correctly. 3. If not, recheck the DDR initialization sequence and whether the DDR has been correctly soldered onto the board. <p>It is also recommended that users recheck the schematic to ensure that the DDR memory has been connected to the i.MX6 correctly.</p> | | |
|---|---|--|--|

Chapter 5

Understanding the IBIS Model

5.1 Overview

This chapter explains how to use the IBIS (input output buffer information specification) model, which is an Electronic Industries Alliance standard for the electronic behavioral specifications of integrated circuit input/output analog characteristics. The model is generated in ASCII text format and consists of multiple tables that capture current vs. voltage (IV) and voltage vs. time (VT) characteristics of each buffer. IBIS models are generally used to perform PCB-board-level signal integrity (SI) simulations and timing analyses.

The IBIS model's features are as follows:

- Supports fast chip-package-board simulation, with SPICE-level accuracy and faster than any transistor-level model
- Provides the following for portable model data
 - I/O buffers, series elements, terminators
 - Package RLC parasitics
 - Electrical board description

5.2 IBIS structure and content

An IBIS file contains the data required to model a component's input, output, and I/O buffers behaviorally in ASCII format. The basic IBIS file contains the following data:

- Header information regarding the model file
- Information about the component, the package's electrical characteristics, and the pin-to-buffer model mapping (in other words, which pins are connected to which buffer models)
- The data required to model each unique input, output, and I/O buffer design on the component

IBIS models are component-centric, meaning they allow users to model an entire component rather than only a particular buffer. Therefore, in addition to the electrical characteristics of a component's buffers, an IBIS file includes the component's pin-to-buffer mapping and the electrical parameters of the component's package.

5.3 Header Information

The first section of an IBIS file provides the basic information about the file and its data. The following table explains the header information notation.

Table 5-1. Header Information

| Keyword | Required | Description |
|----------------|----------|--|
| [IBIS Ver] | Yes | Version of IBIS Specification this file uses. |
| [Comment char] | No | Change the comment character. Defaults to the pipe () character |
| [File Name] | Yes | Name of this file. All file names must be lower case. The file name extension for an IBIS file is .ibs |
| [File Rev] | Yes | The revision level of this file. The specification contains guidelines for assigning revision levels. |
| [Date] | No | Date this file was created |
| [Source] | No | The source of the data in this file. Data is taken from a simulation and validated on the board. |
| [Notes] | No | Component or file-specific notes. |
| [Disclaimer] | No | May be legally required |
| [Copyright] | No | The file's copyright notice |

Header Information

```
[IBIS Ver] 4.2
[Comment Char] |_char
[File Name] mx6sx_bga19x19_consmr.ibs [File Rev] 20140807
[Date] Fri Aug 8 09:44:31 2014
[Source] FSL Viper 2014.01.29 [Notes]
```

5.4 Component and pin information

The second section of an IBIS file is where the data book information regarding the component's pinout, pin-to-buffer mapping, and the package and pin electrical parameters is placed.

Table 5-2. Component and Pin Information

| Keyword | Required | Comment |
|------------------|----------|--|
| [Component] | Yes | The name of the component being modeled. Standard practice has been to use the industry standard part designation. Note that IBIS files may contain multiple [Component] descriptions. |
| [Manufacturer] | Yes | The name of the component manufacturer |
| [Package] | Yes | This keyword contains the range (minimum, typical and maximum values) over which the packages' lead resistance, inductance, and capacitance vary (the R_pkg, L_pkg, and C_pkg parameters). |
| [Pin] | Yes | This keyword contains the pin-to-buffer mapping information. In addition, the model creator can use this keyword to list the package information: R, L, and C data for each individual pin (R_pin, L_pin, and C_pin parameters). |
| [Package Model] | No | If the component model includes an external package model (or uses the [Define Package Model] keyword within the IBIS file itself), this keyword indicates the name of that package model. |
| [Pin Mapping] | No | This keyword is used if the model creator wishes to include information on buffer power and ground connections. This information may be used for simulations involving multiple outputs switching. |
| [Diff Pin] | No | This keyword is used to associate buffers that should be driven in a complementary fashion as a differential pair. |
| [Model Selector] | | This keyword provides a simple means by which several buffers can be made optionally available for simulation at the same physical pin of the component. |

Component and pin information

```

[Component]      mx6sx_bga19x19
[Manufacturer]    NXP
[Package]
| variable      typ          min          max
R_pkg           0.2839146     0.0091798    0.575946
L_pkg           3.33311nH       0.16746nH    7.75079nH
C_pkg           24.5630pF         1.13795pF    356.1pF
|
[Pin] signal_name  model_name  R_pin      L_pin      C_pin
A1    VSS          GND        NA          NA          NA
A2    DRAM_SDQS3_N ddr        0.473559    5.48846nH  1.36964pF
A3    DRAM_SDQS3_P ddr        0.478764    5.40998nH  1.61263pF

```

Model information

```

|
[Pin Mapping]      pulldown_ref      pullup_ref
A1                 VSS                NC
A2                 NC                NC
...
|
[Diff Pin]         inv_pin           vdiff          tdelay_typ  tdelay_min  tdelay_max
A3                 A2                NA            NA           NA           NA
H1                 H2                NA            NA           NA           NA
M2                 M1                NA            NA           NA           NA
T1                 U1                NA            NA           NA           NA
AB2                AC2                NA            NA           NA           NA
|
*****
*      Model Selector      *
*****
|
[Model Selector] ddr
ddr3_sel11_ds111_mio      DDR, 1.5V, ddr3 mode, 34 Ohm driver impedance
ddr3_sel11_ds110_mio      DDR, 1.5V, ddr3 mode, 40 Ohm driver impedance

```

5.5 Model information

The [Model] keyword starts the description of the data for a particular buffer.

Table 5-3. Model information

| Keyword | Comment |
|--|--|
| [Model Spec] | General set of parameters for the model simulation. |
| [Receiver Thresholds] | Threshold information for the different simulation cases. |
| [Temperature Range] | The temperature range over which the min, typ and max IV and switching data have been gathered. |
| [Voltage Range] | The range over which Vcc is varied to obtain the min, typ and max pullup and power clamp data. |
| [Pulldown] [Pullup] [GND_clamp] [POWER_clamp] | IV information. For more details, see “IV information” . |
| [Ramp] [Rising Waveform] [Falling Waveform] | VT information. For more details, see “VT information” . |
| [Test Data] [Rising Waveform Near] [Rising Waveform Far] [Falling Waveform Near] [Falling Waveform Far] | VT golden model information. For more details, see “Golden Model VT information” . |
| [Test Load] | |

5.5.1 IV information

IV information is composed of four Current-over-Voltage tables: [Pullup], [Pulldown], [GND_clamp], and [Power_clamp]. Each look-up table describes a different part of the IO cell model.

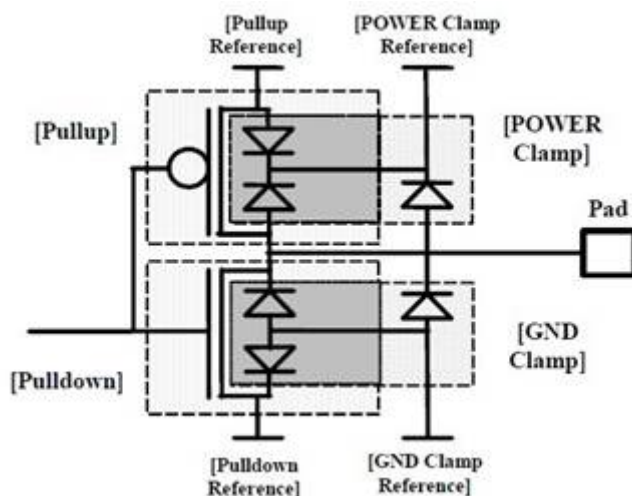


Figure 5-1. Model IV parameters' structure

5.5.2 VT information

Table 5-4. Ramp and waveform keywords

| Keyword | Required | Comment |
|--------------------|----------|--|
| [Ramp] | Yes | <p>Basic ramp rate information, given as a dV/dt_r for rising edges and dV/dt_f for falling edges, see the following equation.</p> $\frac{dV}{dt} = \frac{20\% \text{ to } 80\% \text{ voltage swing}}{\text{time taken to swing above voltage}}$ <p>Note: The dV value is the 20% to 80% voltage swing of the buffer when driving into the specified load, R_{load} (for [Ramp], this load defaults to 50). For CMOS drivers or I/O buffers, this load is assumed to be connected to the voltages defined by the [Voltage Range] keyword for falling edges and to ground for rising edges.</p> |
| [Rising Waveform] | No | The actual rising (low to high transition) waveform, provided as a VT table. |
| [Falling Waveform] | No | The actual falling (high to low transition) waveform, provided as a VT table. |

Table 5-5. Ramp and waveform keywords example

| | | |
|--------------------------|----------------|----------------|
| [Ramp] | | |
| I variable typ | min | max |
| dV/dt_r 0.4627/0.3456n | 0.4326/0.4568n | 0.4962/0.3030n |
| dV/dt_f 0.4546/0.3481n | 0.4272/0.3918n | 0.4774/0.3569n |

Table continues on the next page...

Table 5-5. Ramp and waveform keywords example (continued)

| | | |
|---------------------|-----------|-----------|
| R_load = 0.2400k | | |
| I | | |
| [Rising Waveform] | | |
| R_fixture= 0.2400k | | |
| V_fixture= 0.0 | | |
| V_fixture_min= 0.0 | | |
| V_fixture_max= 0.0 | | |
| Itime V(typ) | V(min) | V(max) |
| I | | |
| I0.0S 0.3369uV | 12.4052uV | 41.7335nV |
| I19.7866fS 0.6730uV | 12.7375uV | 0.3823uV |
| I20.8863fS 0.6917uV | 12.7519uV | 0.4013uV |
| I21.9489fS 0.7058uV | 12.7657uV | 0.4196uV |
| ... | | |
| I | | |
| [Falling Waveform] | | |
| R_fixture= 0.2400k | | |
| V_fixture= 0.0 | | |
| V_fixture_min= 0.0 | | |
| V_fixture_max= 0.0 | | |
| Itime V(typ) | V(min) | V(max) |
| I | | |
| I0.0S 0.7711V | 0.7211V | 0.8270V |
| I0.3334nS 0.7711V | 0.7211V | 0.8270V |
| I0.3445nS 0.7711V | 0.7211V | 0.8269V |
| ... | | |

The [Ramp] keyword is always required, even if the [Rising Waveform] and [Falling Waveform] keywords are used. However, the VT tables under [Rising Waveform] and [Falling Waveform] are generally preferred to [Ramp] for the following reasons:

- VT data may be provided under a variety of loads and termination voltages
- VT tables may be used to describe transition data for devices as they turn on and turn off.
- [Ramp] effectively averages the transitions of the device, without providing any details on the shapes of the transitions themselves. All detail of the transition ledges would be lost.

The VT data should be included under two [Rising Waveform] and two [Falling Waveform] sections, each containing data tables for a Vcc-connected load and a Ground-connected load (although other loading combinations are permitted).

The most appropriate load is a resistive value corresponding to the impedance of the system transmission lines the buffer will drive (own impedance). For example, a buffer intended for use in a 60 Ω system is best modeled using a 60 Ω load (R_fixture).

- I_down [GND clamp] + [Power clamp] + [Pulldown]
- I_up [GND clamp] + [Power clamp] + [Pullup]
- I_recvr [GND clamp] + [Power clamp]

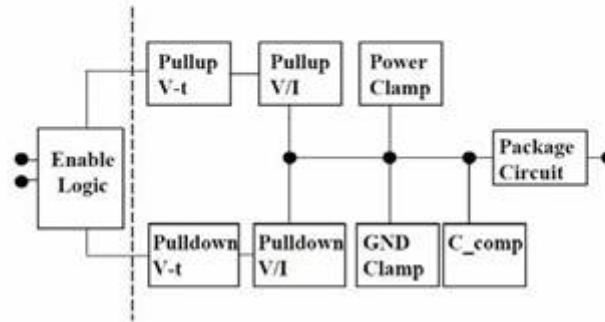


Figure 5-2. Model data interpretation

5.5.3 Golden Model VT information

Golden waveforms are a set of waveforms simulated using known ideal test loads. They are useful for verifying the accuracy of behavioral simulation results against the transistor level circuit model from which the IBIS model parameters originated.

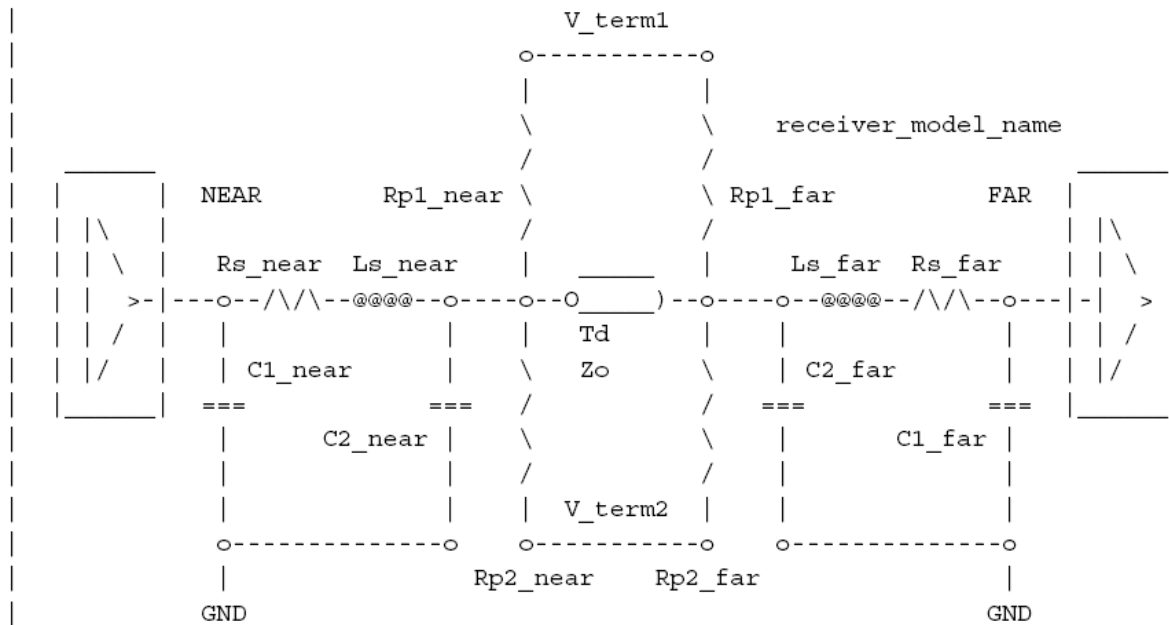


Figure 5-3. Generic test load network

Table 5-6. Golden waveform keywords

| Keyword | Required | Comment |
|---|----------|--|
| [Test Data] | No | <ul style="list-style-type: none"> Provides a set of golden waveforms and references the conditions under which they were derived. Useful for verifying the accuracy of behavioral simulation results against the transistor level circuit model from which the IBIS model parameters originated. |
| [Rising Waveform Near] [Rising Waveform Far] [Falling Waveform Near] [Falling Waveform Far] | Yes | Current-Over-Voltage tables, for far and near portions of the golden model as described by Figure 5-3 . |
| [Test Load] | Yes | <ul style="list-style-type: none"> Defines a test load network and its associated electrical parameters for reference by golden waveforms under the [Test Data] keyword. If Test_load_type is Differential, the test load is a pair of the circuits shown in . If the R_diff_near or R_diff_far subparameter is used, a resistor is connected between the near or far nodes of the two circuits. If Test_load_type is Single_ended, R_diff_near and R_diff_far are ignored. |

5.6 NXP naming conventions for model names and usage in i.MX6 IBIS file

The model names are defined per each [Model selector]. The models may differ from each other by having different parameters—such as voltage, drive strength, mode of operation, and slew rate. The mode of operation, drive strength, and slew rate parameters are programmable by software.

5.6.1 [Model Selector] ddr

The “ddr” model type supports the DDR signals.

5.6.2 DDR [Model Selector]

“ddr” models exist for DDR3, DDR3L, DDR3U and LPDDR2 protocols.

This model has the following parameters:

- DDR protocol
- DDR IO type
- Drive strength
- ODT enable/disable

The IBIS model name is composed from the parameters' values in two ways, as follows:

- Without active ODT circuit: <ddr protocol>_sel<ddr_type>_ds<drive_strength>_mio
- With active ODT circuit: <ddr protocol>odt_t<ODT_value>_sel<ddr_type>_mi

DDR write models (“_mio” suffix) have no simulated ODT, as ODT is disabled during write. Write models' DS parameter is meaningful and changes to describe the different levels of drive strength.

DDR read models (“_mi” suffix) have no meaningful DS parameter, as no driving happens during read. Read models' ODT parameter is meaningful and changes to describe different levels of ODT impedance.

DDR Protocol Selected according to the used DDR. DDR IO voltage level is selected accordingly.

DDR IO Type Controlled by the IOMUXC_SW_PAD_CTL_GRP_DDR_TYPE[19:18] register in IOMUXC (IOMUX controller) DDR_SEL bits, to select between DDR3 & LPDDR2.

Drive strength Controlled by bits [5:3] (DSE) of the following registers in IOMUXC (IOMUX controller):

IOMUXC_SW_PAD_CTL_GRP_BxDS (4 registers)

IOMUXC_SW_PAD_CTL_GRP_CTLDS

IOMUXC_SW_PAD_CTL_PAD_DRAM_ADDRxx (16 registers)

IOMUXC_SW_PAD_CTL_PAD_DRAM_DQMx (4 registers)

IOMUXC_SW_PAD_CTL_PAD_DRAM_RAS_B

IOMUXC_SW_PAD_CTL_PAD_DRAM_CAS_B

IOMUXC_SW_PAD_CTL_PAD_DRAM_CSx_B (2 registers)

IOMUXC_SW_PAD_CTL_PAD_DRAM_SDWE_B

IOMUXC_SW_PAD_CTL_PAD_DRAM_ODTx (2 registers)

IOMUXC_SW_PAD_CTL_PAD_DRAM_SDBAx (3 registers)

IOMUXC_SW_PAD_CTL_PAD_DRAM_SDCKE0 (2 registers)

IOMUXC_SW_PAD_CTL_PAD_DRAM_SDCLK0_P

IOMUXC_SW_PAD_CTL_PAD_DRAM_SDQS0_P (4 registers)

IOMUXC_SW_PAD_CTL_PAD_DRAM_RESET

ODT value Controlled by bits [18:16], [14:12], [10:8], and [6:4] in MPODTCTRL register of MMDC.

[Model Selector] DDR in IBIS file

```
ddr3_sel111_ds111_mio          DDR, 1.5V, ddr3 mode, 34 Ohm driver impedance
...
lpddr2_sel110_ds111_mio       LPDDR, 1.2V, lpddr2 mode, 34 Ohm driver impedance
...
```

See the register description in the IOMUXC chapter in the chip reference manual for further details about this model.

5.6.3 RGMII

This model has the following parameters:

- RGMII voltage
- Drive strength

The IBIS model name is composed from the parameters' values as follows:

```
rgmii1p8_sel11_ds<drive_strength>_mio
```

```
rgmii2p5_sel11_ds<drive_strength>_mio
```

Voltage Level IBIS currently supports 2.5 V and 1.8 V options. 2.5 V or 1.8V is applied to NVCC_RGMIIx..

Drive strength Controlled by bits [5:3] (DSE) of the following registers in IOMUXC (IOMUX controller):

IOMUXC_SW_PAD_CTL_PAD_RGMII_TXC

IOMUXC_SW_PAD_CTL_PAD_RGMII_TX_CTL

IOMUXC_SW_PAD_CTL_PAD_RGMII_TD_x (4 registers)

IOMUXC_SW_PAD_CTL_PAD_RGMII_RXC

IOMUXC_SW_PAD_CTL_PAD_RGMII_RX_CTL

IOMUXC_SW_PAD_CTL_PAD_RGMII_RD_x (4 registers)

[Model Selector] RGMII in IBIS file

| | |
|--------------------------|--|
| rgmii1p8_sel11_ds111_mio | DDR, 1.8V, ddr3 mode, 32/29 Ohm pd/pu driver impedance |
| rgmii1p8_sel11_ds110_mio | DDR, 1.8V, ddr3 mode, 37/34 Ohm pd/pu driver impedance |
| rgmii1p8_sel11_ds101_mio | DDR, 1.8V, ddr3 mode, 45/41 Ohm pd/pu driver impedance |

5.6.4 [Model Selector] GPIO

This model has the following parameters:

- Voltage level
- Drive strength
- Slew rate
- Speed

The IBIS model name is composed from parameters' values as follows:

```
gpio<voltage_level>_ds<drive_strength>_sr<slew_rate(1 bit)><speed(2 bits)>_mio
```

Voltage level For i.MX6 chips, there are no user configurations for the voltage level because the GPIO cell senses the NVCC and auto-configures itself accordingly. The IBIS user can choose between high and low voltage by selecting a different model at [Model Selector].

Drive strength Controlled by the DSE bits (bits [5:3]) in the

IOMUXC_SW_PAD_CTL_PAD_<pad name>.

Slew rate Controlled by the SRE bit (bit 0) in the IOMUXC_SW_PAD_CTL_PAD_<pad name>.

Speed Controlled by the SPEED bits (bits [7:6]) in the IOMUXC_SW_PAD_CTL_PAD_<pad name>.

[Model Selector] gpio in IBIS file

```

gpio1p2_ds111_sr111_mio GPIO, 1.2 V,extra drive,fast sr,max fsel
gpio1p2_ds111_sr110_mio GPIO, 1.2 V,extra drive,fast sr,fast fsel
gpio1p2_ds111_sr101_mio GPIO, 1.2 V,extra drive,fast sr,medium fsel
...
gpio1p5_ds111_sr111_mio GPIO, 1.5V,extra drive,fast sr,max fsel
gpio1p5_ds111_sr110_mio GPIO, 1.5V,extra drive,fast sr,fast fsel
gpio1p5_ds111_sr101_mio GPIO, 1.5V,extra drive,fast sr,medium fsel
...
gpio1p8_ds111_sr111_mio GPIO, 1.8V,extra drive,fast sr,max fsel
gpio1p8_ds111_sr110_mio GPIO, 1.8V,extra drive,fast sr,fast fsel
gpio1p8_ds111_sr101_mio GPIO, 1.8V,extra drive,fast sr,medium fsel
gpio1p8_ds111_sr100_mio GPIO, 1.8V,extra drive,fast sr,slow fsel
...
gpio2p5_ds111_sr111_mio GPIO, 2.5V,extra drive,fast sr,max fsel
gpio2p5_ds111_sr110_mio GPIO, 2.5V,extra drive,fast sr,fast fsel
gpio2p5_ds111_sr101_mio GPIO, 2.5V,extra drive,fast sr,medium fsel
...
gpio3p3_ds111_sr111_mio GPIO, 3.3V,extra drive,fast sr,max fsel
gpio3p3_ds111_sr110_mio GPIO, 3.3V,extra drive,fast sr,fast fsel
gpio3p3_ds111_sr101_mio GPIO, 3.3V,extra drive,fast sr,medium fsel
...

```

See the register description in the IOMUXC chapter in the chip reference manual for further details about this model.

5.6.5 [Model Selector] LVDS

At the time of publication, i.MX 6SoloX IBIS does not contain the LVDS model. It is expected to be published in a future revision.

5.6.6 [Model Selector] USB

At the time of publication, i.MX6 IBIS does not contain the USB model. It is expected to be published in a future revision.

5.6.7 List of pins not modeled in the i.MX6 IBIS file

The following table provides a list of analog or special interface pins that are not modeled in the i.MX 6SoloX IBIS file.

Table 5-7. i.MX 6SoloX pins not supported by IBIS

| ANALOG | LVDS | PCle | USB |
|------------|--------------|-----------|----------------|
| GPANAIO | LVDS_CLK_N | PCIE_RX_N | USB_OTG1_CHD_B |
| CCM_CLK2 | LVDS_CLK_P | PCIE_RX_P | USB_OTG1_VBUS |
| CCM_CLK1_N | LVDS_DATA3_N | PCIE_TX_N | USB_OTG2_VBUS |
| CCM_CLK1_P | LVDS_DATA3_P | PCIE_TX_P | USB_OTG1_DN |
| RTC_XTALI | LVDS_DATA2_N | — | USB_OTG2_DN |
| RTC_XTALO | LVDS_DATA2_P | — | USB_OTG1_DP |
| XTALI | LVDS_DATA1_N | — | USB_OTG2_DP |
| XTALO | LVDS_DATA1_P | — | — |
| — | LVDS_DATA0_N | — | — |
| — | LVDS_DATA0_P | — | — |

5.7 Quality assurance for the IBIS models

The IBIS models are validated against the IBIS specification, which provides a way to objectively measure the correlation of model simulation results with reference transistor-level spice simulation or measurements.

Correlation The process of making a quantitative comparison between two sets of I/O buffer characterization data, such as lab measurement vs. structural simulation or behavioral simulation vs. structural simulation.

Correlation Level A means for categorizing I/O buffer characterization data based on how much the modeling engineer knows about the processing conditions of a sample component and which correlation metric he or she used.

All models have passed the following checks:

- IBISCHK without errors or unexplained warnings
- Data for basic simulation checked
- Data for timing analysis checked
- Data for power analysis checked
- Correlated against Spice simulations

5.8 IBIS usage

NXP board designers used the i.MX6Q IBIS model with the Hyperlynx tool by Mentor Graphics. The HyperLynx version used was HyperLynx v8.1.1 + Update 2.

Effective board design results achieved after loading:

- i.MX6Q IBIS model.
- Companion IC IBIS models.
- Board model in HyperLynx format.

Board simulations for various GPIO, LVDS, and DDR signals were then run.

5.9 References

Consult the following references for more information about the IBIS model.

- IBIS Open Forum (<http://ibis.org/>)

The IBIS Open Forum consists of EDA vendors, computer manufacturers, semiconductor vendors, universities, and end-users. It proposes updates and reviews, revises standards, and organizes summits. It promotes IBIS models and provides useful documentation and tools.

- IBIS specification

Chapter 6

Using the Manufacturing Tool

6.1 Overview

The i.MX manufacturing tool is designed to program firmware onto storage devices such as NAND or eSDe through the EVK and preload the data area with media files in an efficient and convenient manner. It is intended for NXP Semiconductor customers or their OEMs who plan to mass manufacture i.MX-based products.

The application is not designed to test the devices or to diagnose manufacturing problems. Devices initialized with this application still need to be functionally verified.

6.2 Feature summary

The tool includes the following features:

- Continuous operation—operations automatically begin with the connection of a new device, and multiple operations such as update and copy can be linked together seamlessly.
- Enumeration—static-ID firmware loaded into RAM in recovery-mode prevents Windows® from enumerating every device.
- AutoPlay—various Windows® ‘pop-up’ application and status messages, such as Explorer in Windows® XP and Windows 7.

In addition, the following characteristics improve the tool’s ease of use:

- An independent process bar is set up for each physical USB port.
- The tool begins processing with the connection of the first device detected and allows users to replace each device after completion instead of needing to wait for all devices to complete.
- The tool uses color-based indicators to indicate the work status on each of the ports.
 - Blue indicates the device is being processed.

- Green indicates the device was successfully processed and that the programmed device can be replaced with a new one independent of the of the device's progress.
- Red indicates the device failed to process.

6.3 Version support

Table 6-1. Version support

| Tool | Version requirement |
|--|------------------------|
| i.MX 6SoloX Manufacturing Tool for WinCE | Version 2.3.2 or later |

6.4 Connecting the manufacturing tool to your device

The manufacturing tool can be connected using a USB hub-based physical setup or a direct connection, as described in [“Connecting with a USB hub,”](#) and [“Connecting directly”](#).

6.4.1 Connecting with a USB hub

The following figure shows how to connect the manufacturing tool, using the USB hub-based physical setup.

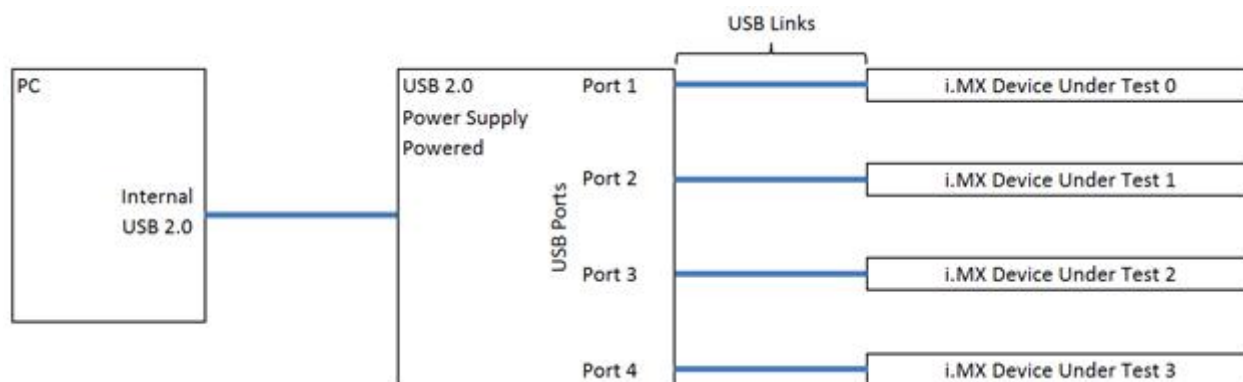


Figure 6-1. Physical connection with a USB hub

Connect an external USB 2.0 powered hub to the PC's USB connection. The hub must meet the following criteria:

- USB 2.0 compliant
- Externally powered and not bus powered.

NOTE

The hub should be able to supply at least 500 mA per USB port.

The PC should recognize the external USB hub. The manufacturing tool will configure the USB ports (up to 16) on the external hub(s) for use.

6.4.2 Connecting directly

The following figure shows the direct connect setup configuration. Each device connects to a single port on an internal PCI USB controller. This configuration is limited to the number of PCI slots available.

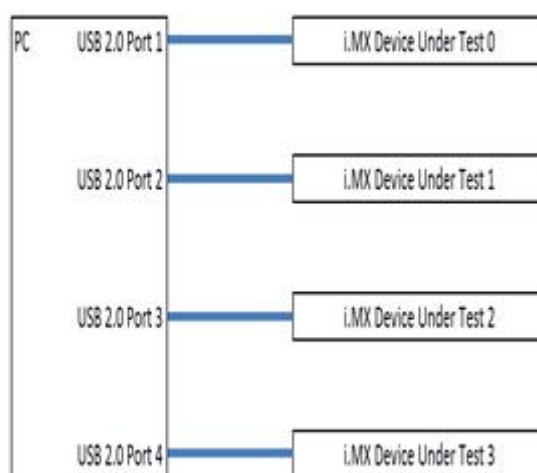


Figure 6-2. Physical connection without a USB hub

6.5 Installing the manufacturing tool

The following subsections explain how to install the manufacturing tool. These subsections are in chronological order.

6.5.1 Running the .exe

The following steps explain where to install the .exe. This executable can be run directly and requires no special installation.

1. Unzip the tool package to your local directory (for example, `D:\mfgtools-rel\`).
2. Find `MfgTool.exe` in the list of files.
3. Run `MfgTool.exe` in your local directory.

You should see a user interface similar to the one shown in the following figure.

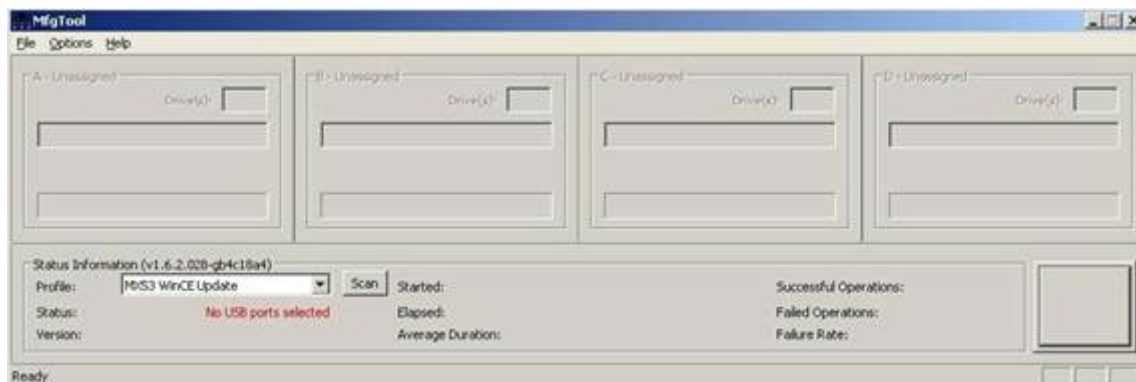


Figure 6-3. Example user interface

6.5.2 Choosing your player profile

The manufacturing tool requires player profiles, which is a directory that contains all the information about a particular product. The player profile includes a configuration file named `player.ini` that specifies the name of the product, USB IDs, SCSI IDs, device firmware files, and media files. The profile also contains a list of one or more player operations to be performed on devices matching the profile. For information about creating and editing profiles, see the *Manufacturing Tool User's Manual*.

The bottom of the user interface includes a status information panel. This panel includes a profile line that displays the currently selected profile, which is called out in the Figure by a red rectangle. Clicking on the arrow opens a dropdown menu that lists the available profiles. Use this list to select your desired platform.

NOTE

The start/stop button in the status information panel (called out by a red circle in the following figure) is disabled until a valid profile is selected.

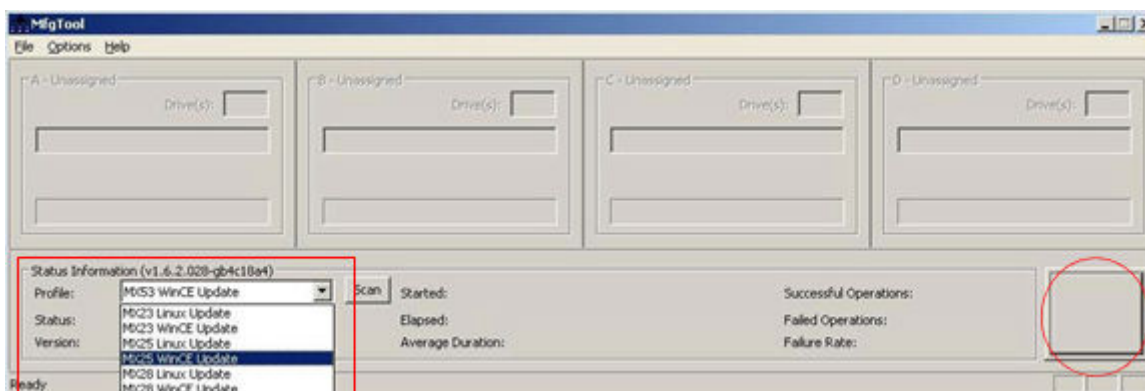


Figure 6-4. Choosing your platform from the profile dropdown menu

6.5.3 Installing the drivers

To install drivers, use the following procedure.

1. Connect your board to one of your PC's USB ports. Make sure you have set the board to bootstrap mode before powering it on. Refer to chip-specific documentation to learn how to set the board to bootstrap mode.
2. When you connect and power on your board, you should see the following pop-window:



Figure 6-5. Default welcome window

3. Choose **Install from a list or specific location** and click **Next**.
4. Input your driver location: `YourDiskVolume:\mfgtools-rel\Drivers\iMX_BulkIO_Driver`

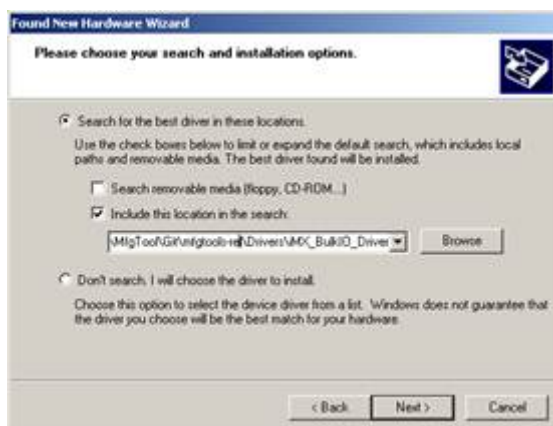


Figure 6-6. Setting your driver location

5. Click **Next**.
6. Click **Finish** to finish the driver installation.



Figure 6-7. Finishing the installation

6.5.4 Configuring your system

There are two ways to configure your system: auto-scanning or using the options menu. To auto-scan the devices connected to your PC, click the scan button on the main window (as shown in [Figure 6-3](#)).

To use the options menu, do the following:

1. Open the options menu at top of the main user interface window.
2. Click configuration to open the configuration window.
3. In the configuration window, click the USB Ports tab; this lets you view all of the USB ports.
4. Select the USB port to which your device is connected (as shown in the following figure) and click **OK** to close the window.

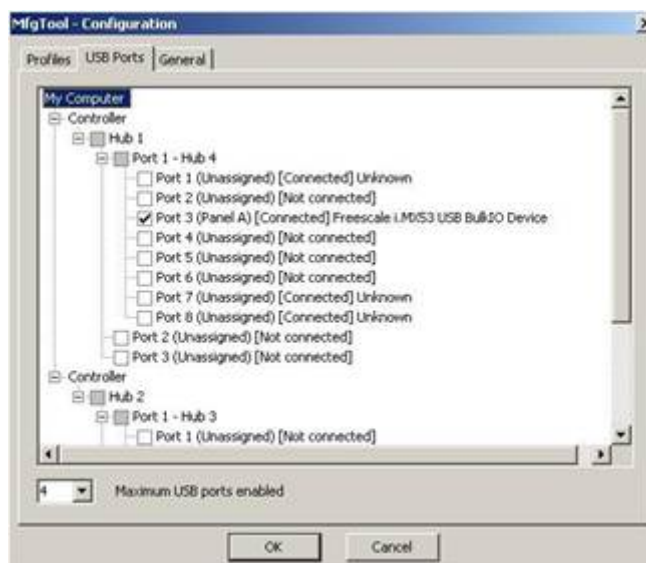


Figure 6-8. Selecting your USB port

6.6 Using the manufacturing tool

Once you have completed all steps in [“Connecting the manufacturing tool to your device,”](#) and [“Installing the manufacturing tool,”](#) the tool is ready for use.

The status information panel is located near the bottom of the main application window (see [Figure 6-3](#)). Use this panel to select a profile and to see the status of the profile and or the firmware version of an update operation. When the tool is idle, the interface appears as in [Figure 6-9](#).

Click the green start button to initiate a process.

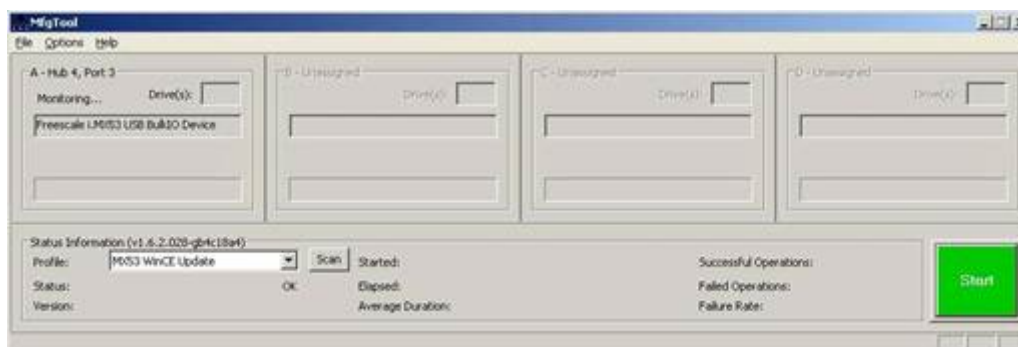


Figure 6-9. Idle interface

Once a process is started, a blue status bar indicates the progress of the processing. The process can be stopped by clicking the red stop button.

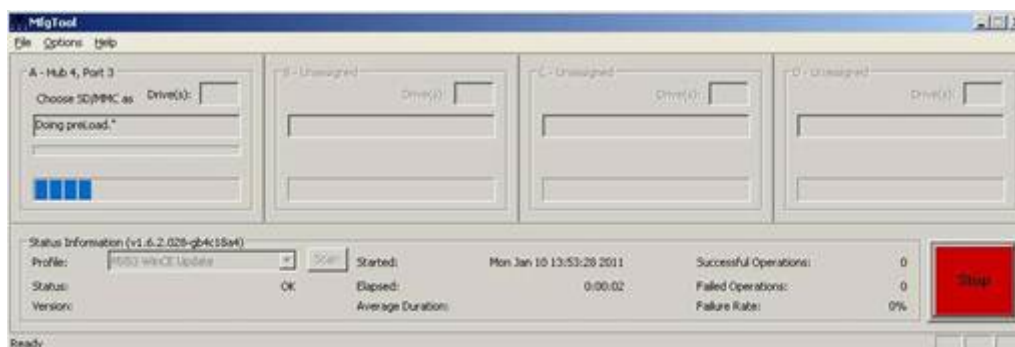


Figure 6-10. Process in progress

If the process completes successfully, the status bar turns green. Click the stop button to finish the process. If the status bar turns red, the processing failed.

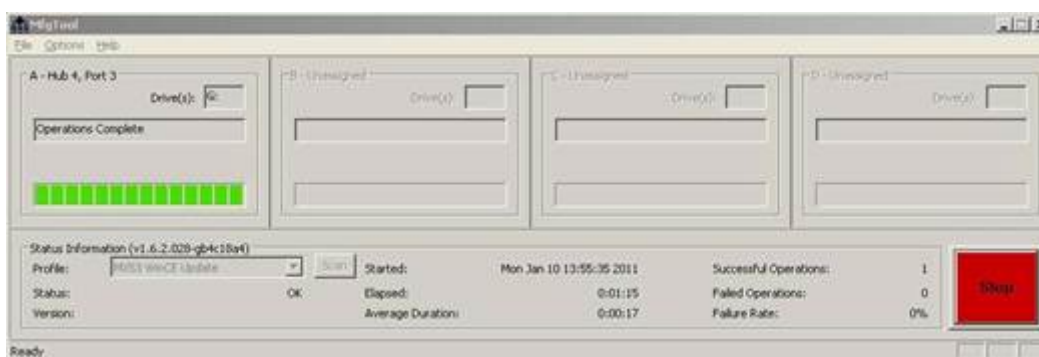


Figure 6-11. Successful process

Once the start/stop button is clicked and the operations begin, the status information panel displays the following information:

Start Time Time the operations began

Elapsed Time How long have operations been running

Average Duration Average time to complete a single device

Successful Operations How many devices successfully updated

Failed Operations How many device updates have failed

Failure Rate Percentage of failures

If you have a terminal tool to monitor the debug serial port of your board, you can open it to see more process information than what is presented in the GUI.

6.7 Customizing the manufacturing tool

This chapter illustrates the tool's behavior with screenshots from the reference design boards provided by NXP. However, you can customize the tool for other designs. For detailed information on customizing the manufacturing tool, see the *Manufacturing Tool User's Manual*

6.8 Other references

For more detailed information about the manufacturing tool, see the following documents included in the manufacturing tool release package. Contact your local NXP sales office for assistance obtaining documents if needed:

- For detailed information about how to use the manufacturing tool, see *Manufacturing Tool V2 Quick Start Guide*.
- For detailed information about how to script the processing operations of the manufacturing tool, see the *Manufacturing Tool V2 UCL User Manual*.
- For information about how to generate the manufacturing tool firmware for Linux and Android, see *Manufacturing Tool V2 Linux or Android Firmware Development Guide*.
- For the change list and known issues, see *Manufacturing Tool V2 Release Notes*.

Chapter 7

Using BSDL for Board-level Testing

7.1 BSDL overview

Boundary scan description language (BSDL) is used for board-level testing after components have been assembled. The interface for this test uses the JTAG pins. The definition is contained within IEEE Std 1149.1.

7.2 How BSDL functions

A BSDL file defines the internal scan chain, which is the serial linkage of the IO cells, within a particular device. The scan chain looks like a large shift register, which provides a means to read the logic level applied to a pin or to output a logic state on that pin. Using JTAG commands, a test tool uses the BSDL file to control the scan chain so that device-board connectivity can be tested.

For example, when using an external ROM test interface, the test tool would do the following:

1. Output a specific set of addresses and controls to pins connected to the ROM
2. Perform a read command and scan out the values of the ROM data pins.
3. Compare the values read with the known golden values.

Based on this procedure, the tool can determine whether the interface between the two parts is connected properly and does not contain shorts or opens.

7.3 Downloading the BSDL file

The BSDL file for each i.MX processor is stored on the NXP website upon product release. Contact your local sales office or fields applications engineer to check the availability of information prior to product releases.

7.4 Pin coverage of BSDL

Each pin is defined as a port within the BSDL file. You can open the file with a text editor (like Wordpad) to review how each pin will function. The BSDL file defines these functions as shown:

```
-- PORT DESCRIPTION TERMS
-- in = input only
-- out = three-state output (0, Z, 1)
-- buffer = two-state output (0, 1)
-- inout = bidirectional
-- linkage = OTHER (vdd, vss, analog)
```

The appearance of "linkage" in a pin's file implies that the pin cannot be used with boundary scan. These are usually power pins or analog pins that cannot be defined with a digital logic state.

7.5 Boundary scan operation

The boundary scan operation is controlled by:

- TEST_MODE, POR_B, and JTAG_MOD pins
- On-chip Fuse bits

The JTAG_MOD pin state controls the selection of JTAG to the core logic or boundary scan operation. See the following references for further information:

- The "System JTAG Controller (SJC)" chapter in the chip reference manual for the definitions of the JTAG interface operations.
- The "JTAG Security Modes" section in the same chapter for an explanation of the operation of the e-Fuse bit definitions in the following table.
- The "Fusemap" chapter in the chip reference manual the fusemap tables.

Table 7-1. System considerations for BSDL

| Pin name | Logic state | Description |
|--------------------|-------------|---------------------------------|
| JTAG_MOD | 1 | IEEE 1149.1 JTAG compliant mode |
| BOOT_MODE[1:0] | [0:0] | Boot From Fuses |
| | [0:1] | Serial Downloader |
| | [1:0] | Internal Boot (Development) |
| POR_B | 1 | Power On Reset for the device |
| e-Fuse bits | | |

Table continues on the next page...

**Table 7-1. System considerations for BSDL
(continued)**

| | | |
|-----------------|-------|-----------------------------------|
| JTAG_SMODE[1:0] | [0:0] | JTAG enable mode |
| | [0:1] | Secure JTAG mode |
| SJC_DISABLE | 0 | Secure JTAG Controller is enabled |

7.6 I/O pin power considerations

The boundary scan operation uses each of the available device pins to drive or read values within a given system. Therefore, the power supply pin for each specific module must be powered in order for the IO buffers to operate. This is straightforward for the digital pins within the system.

PCIe is not a digital interface, but the module provides built-in support for the IEEE 1149.6 extension for AC testing of their pins. Therefore, this module must also be powered when utilizing a scan chain that contains the pins from this module, or the scan chain does not function properly.

Chapter 8

Appendix A Revision History

Table 8-1. Revision History

| Rev. Number | Date | Substantive Change(s) |
|-------------|---------|--|
| 0 | 05/2015 | Initial release |
| 1 | 03/2016 | Corrected the PCIE signals descriptions in Table 2-6 . Updated PCIE supply requirements for boundary scan operation in Table 2-6 . Updated PCIe requirements for unused PCIE signals and the associated note in Table 2-17 . |
| 2 | 10/2019 | Corrected application note reference in Essential reference . Corrected PCIe signal names in Table 2-10 . Updated USB HSIC recommendation in Table 2-11 . Corrected LVDS, PCIe and USB_PTG1_VBUS signal names in Table 2-17 . Removed VADC signal names in Table 2-17 . Converted the Sabre SD board layer stack from a figure to a table to improve readability (Table 3-1). Corrected PCIe signal names in Table 3-9 |



Chapter 9

Appendix B Development Platforms

This appendix provides a complete list of the development platforms that are available from NXP to support the i.MX 6SoloX.

Table 9-1. SABRE Board for Smart Devices

| | |
|------------------------------|---|
| Version i.MX used | i.MX 6SoloX |
| Schematic PN and Rev. | 170-27962 Rev. C |
| Features | <ul style="list-style-type: none">• 1 GByte DDR3L• 512 Mbit QSPI Flash• eMMC Footprint• 1x SD3.0 SD Card Socket• 2x SD2.0 SD Card Sockets• LVDS Port• LCD 24-bit Parallel Port• CSI Camera Connector• Audio Codec• 2x Gbit Ethernet (RJ45)• Mini PCIe• Sensors• Accelerometer• Digital eCompass• Ambient Light Sensor• 2x CAN Ports• 8x 12-bit ADC input Port |
| Quick Start Guide | Available at www.nxp.com/imxsabre on NXP website. |
| Schematic | Available at www.nxp.com/imxsabre on NXP website. |
| Layout | Available at www.nxp.com/imxsabre on NXP website. |



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